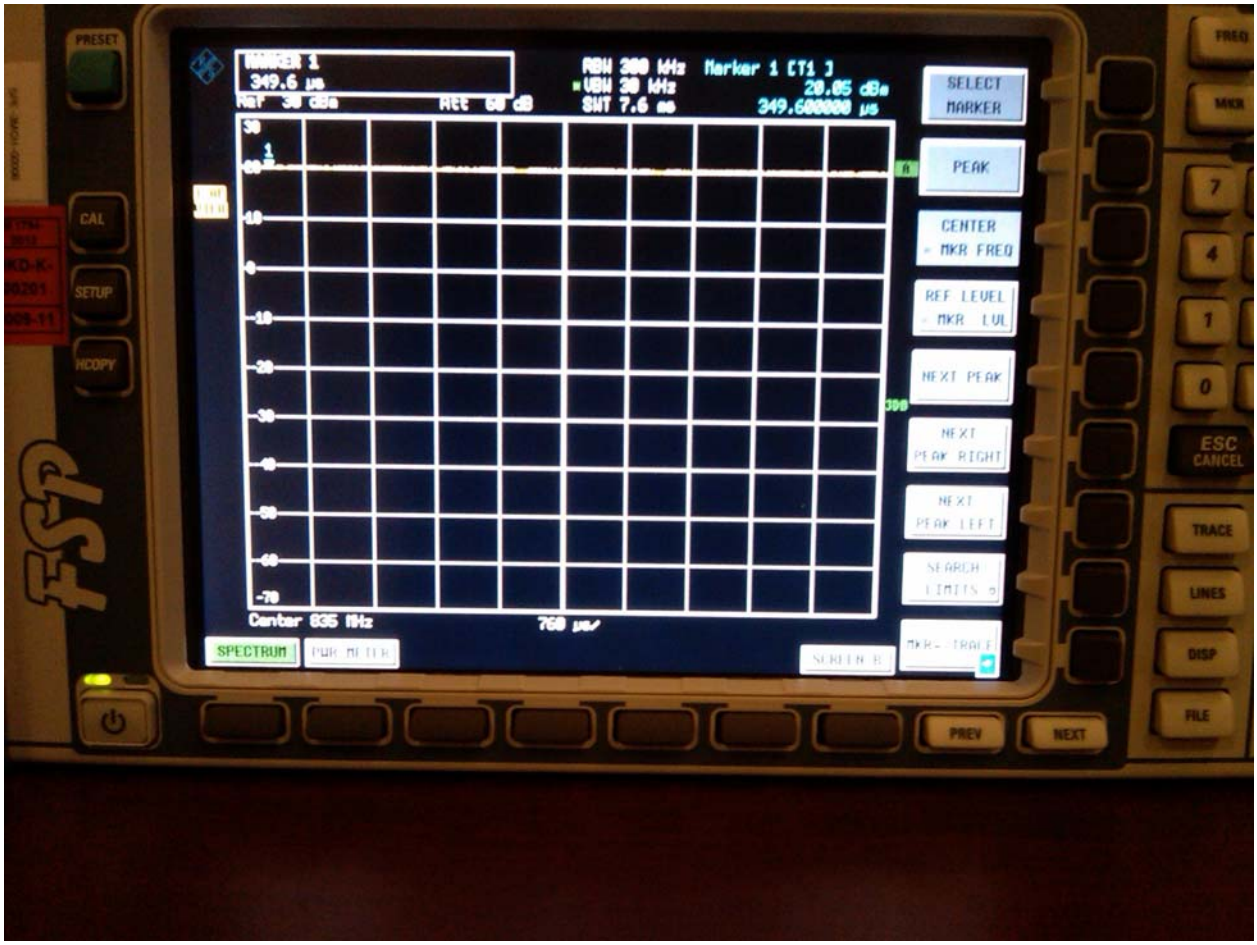
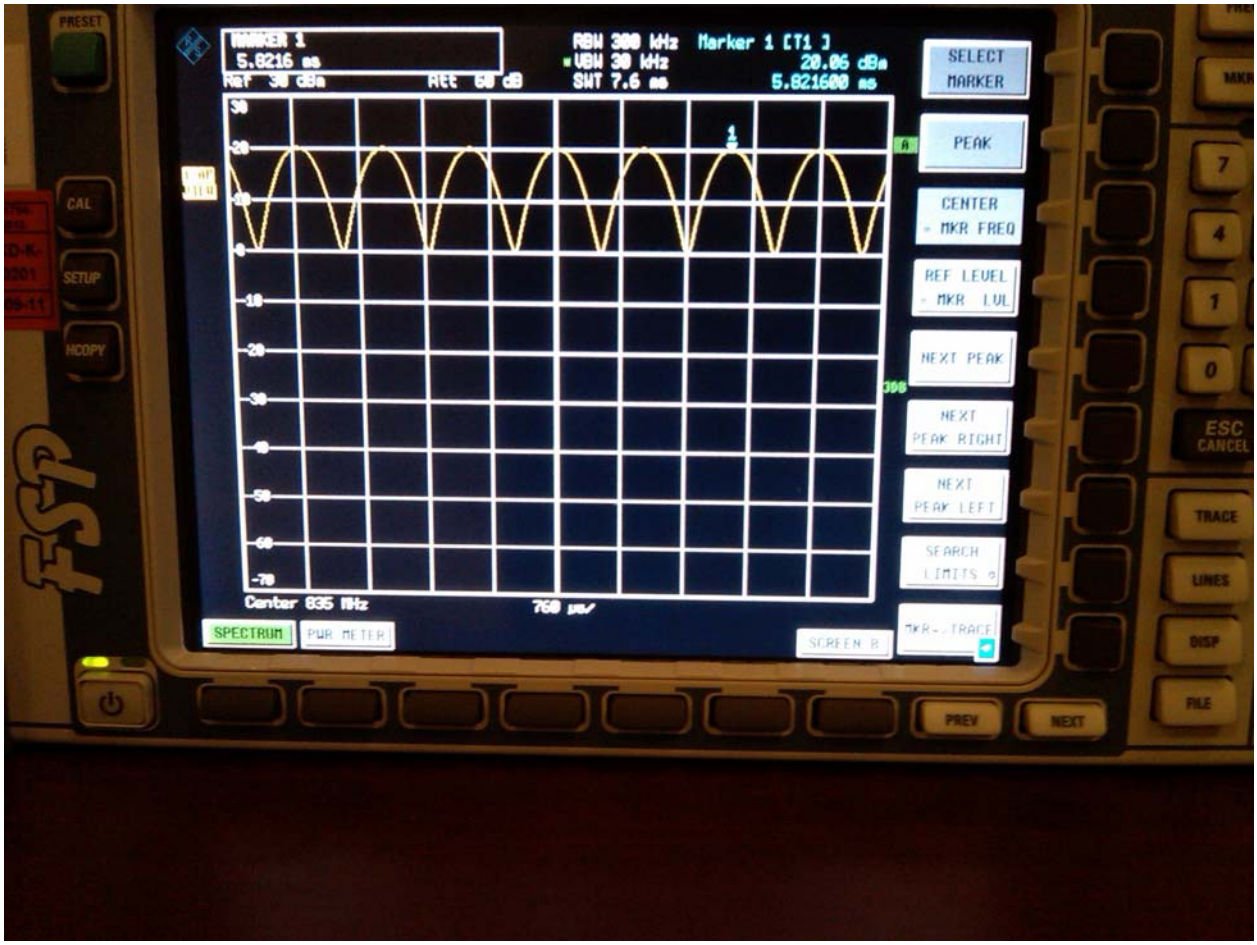
Annex A: Measurement data and plots

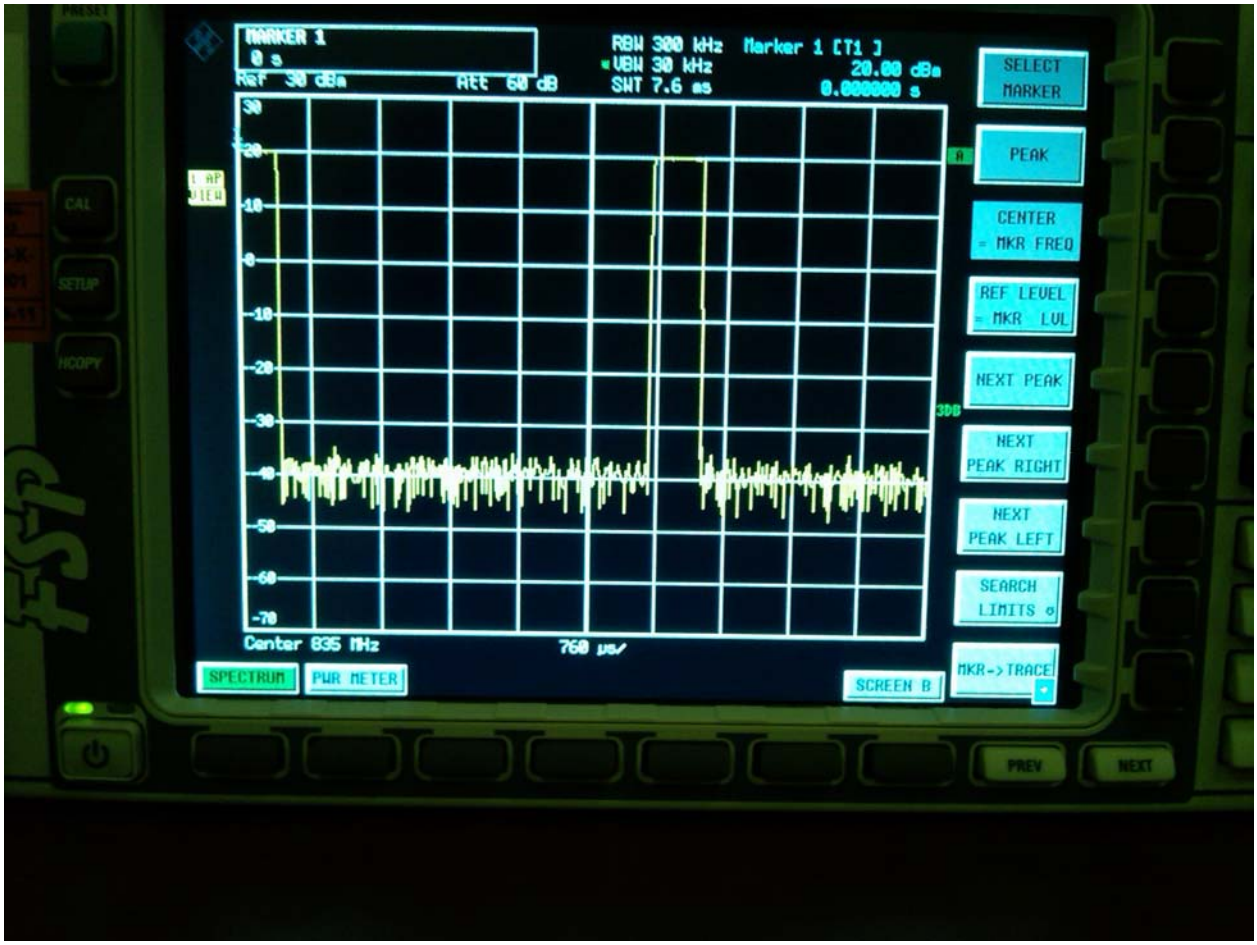
A.1 Spectrum analyser plots: CW, 80%AM, GSM and WCDMA signals



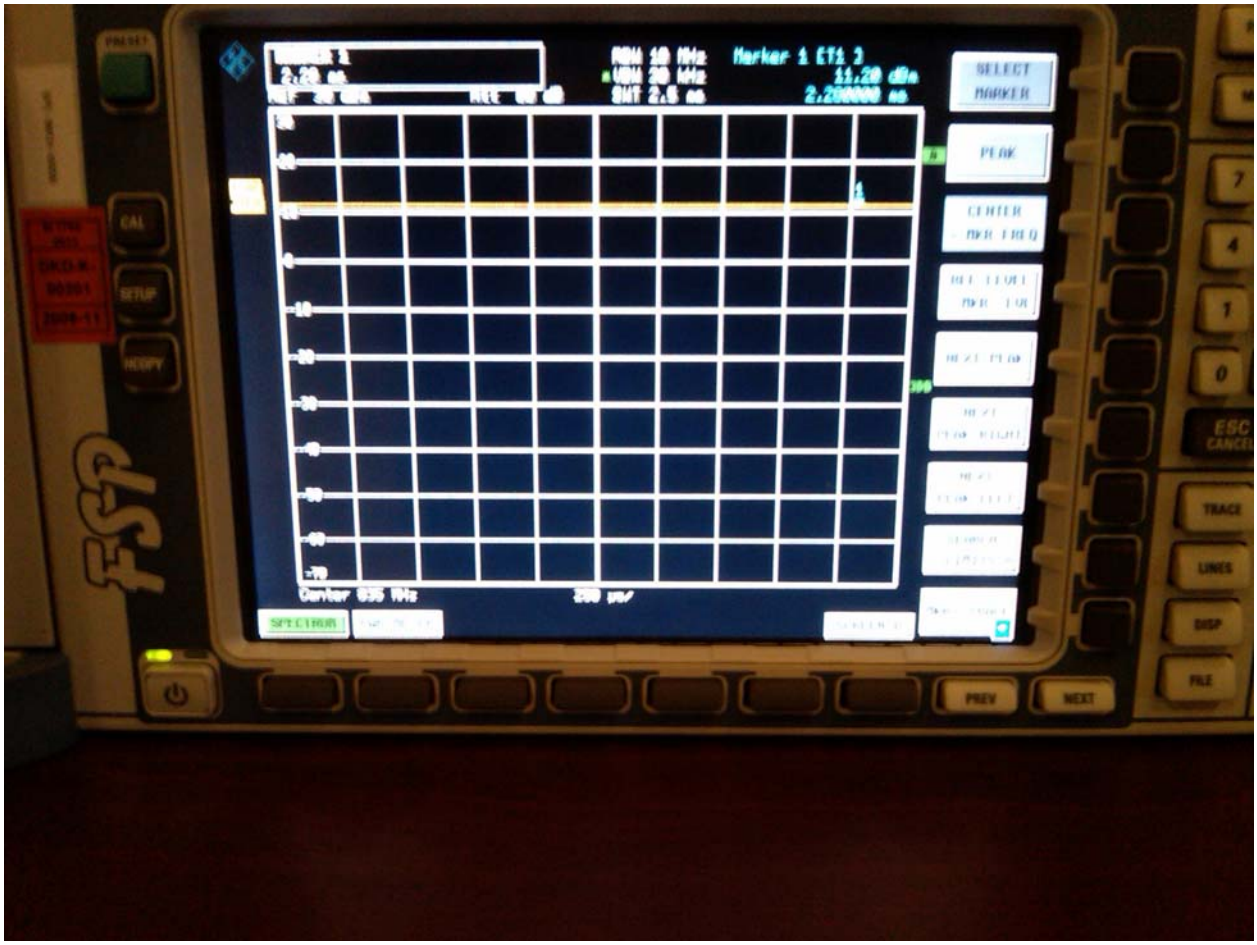
0 Hz Span CW Plot (835MHz)



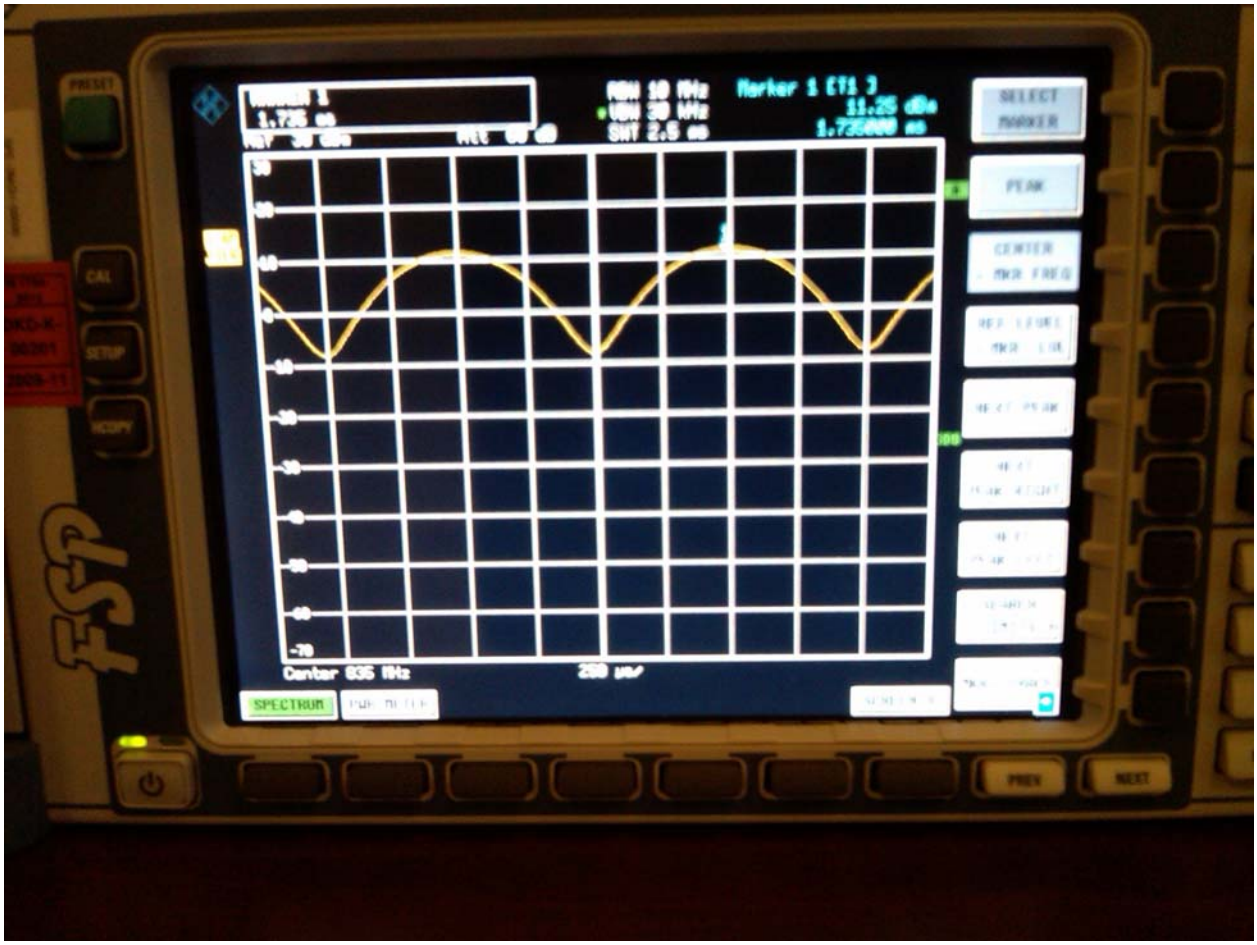
0 Hz Span 80% AM Plot (835MHz)



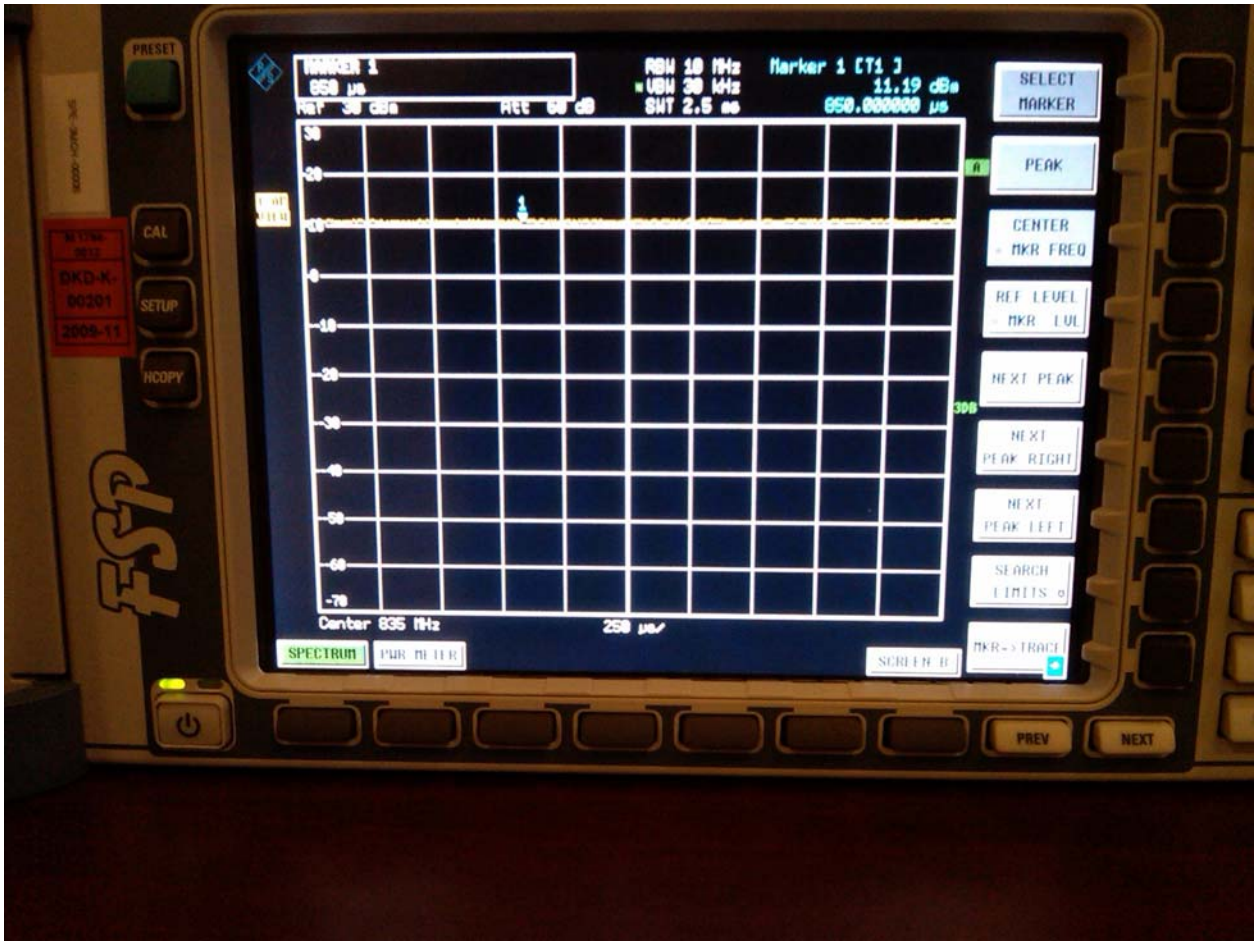
0 Hz Span GSM (835MHz)



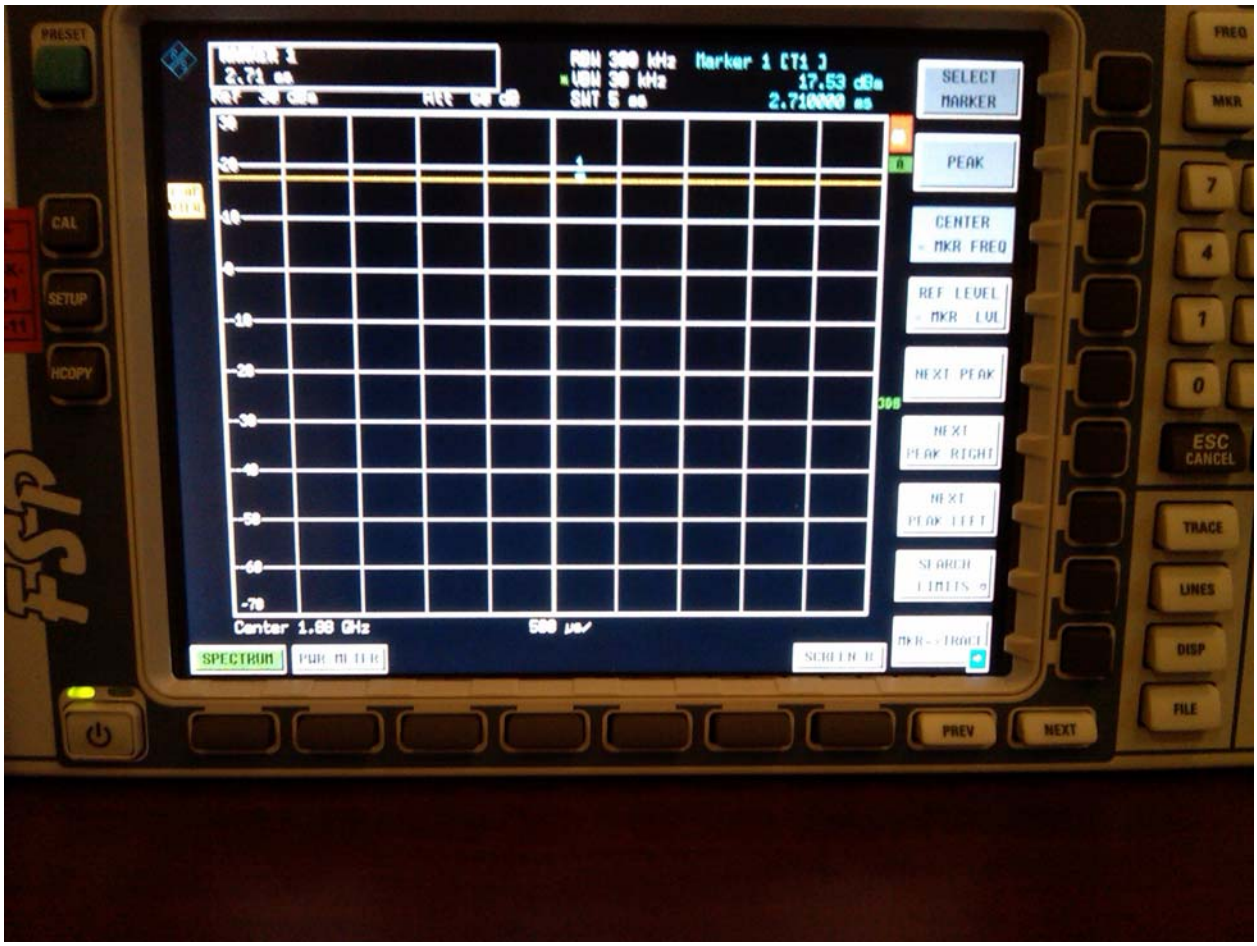
0 Hz Span CW Plot (835MHz)



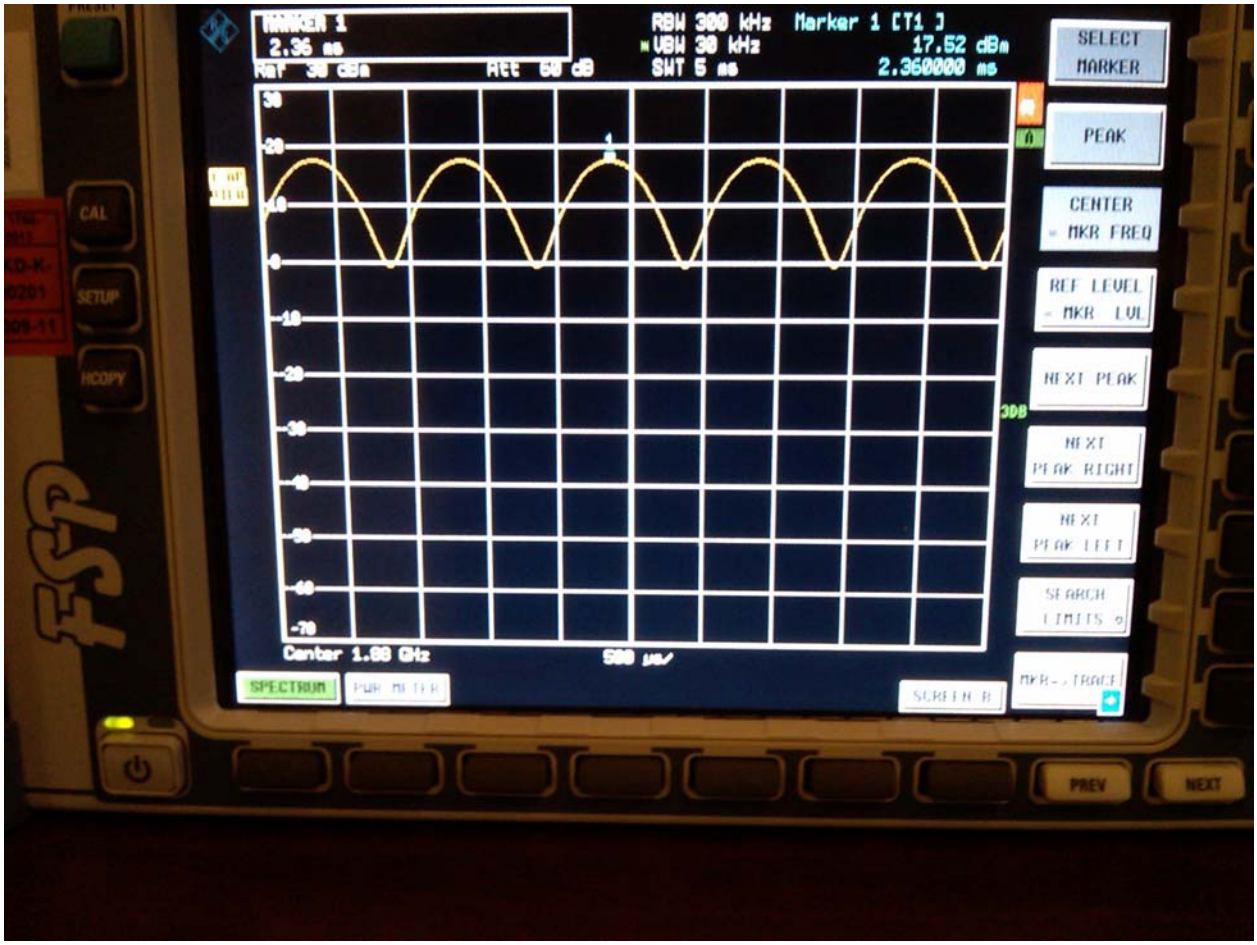
0 Hz Span 80% AM Plot (835MHz)



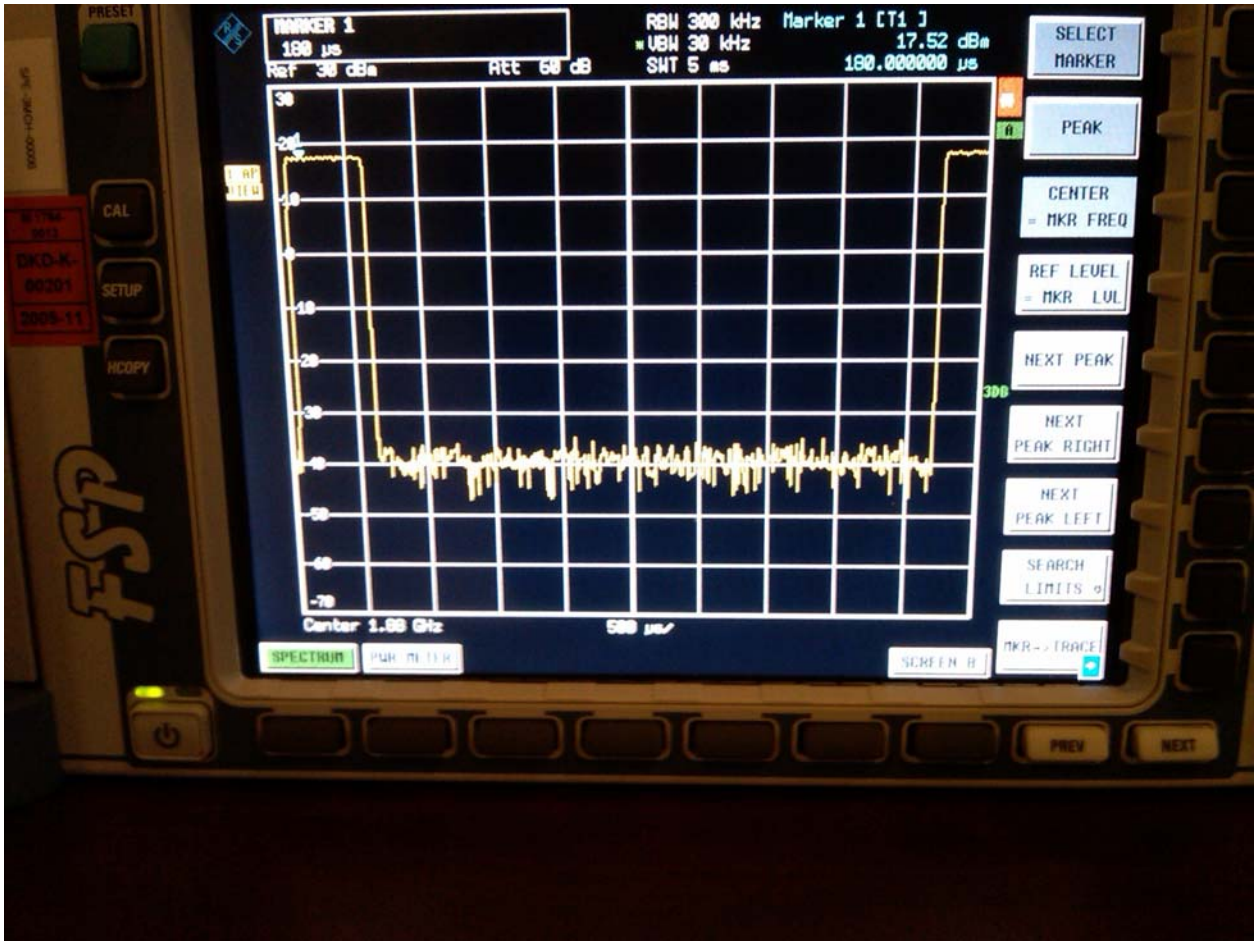
0 Hz Span WCDMA (835MHz)



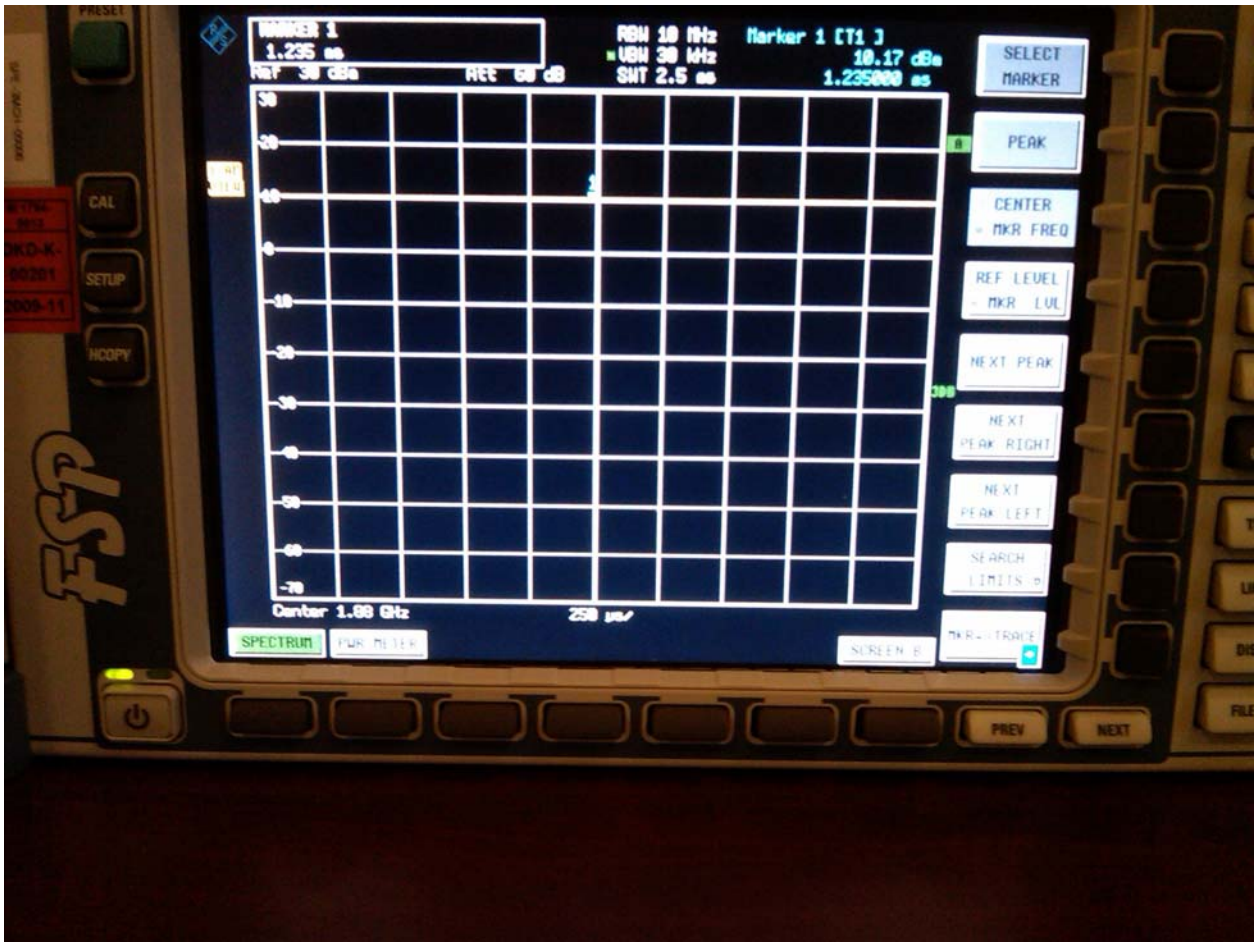
0 Hz Span CW Plot (1880MHz)



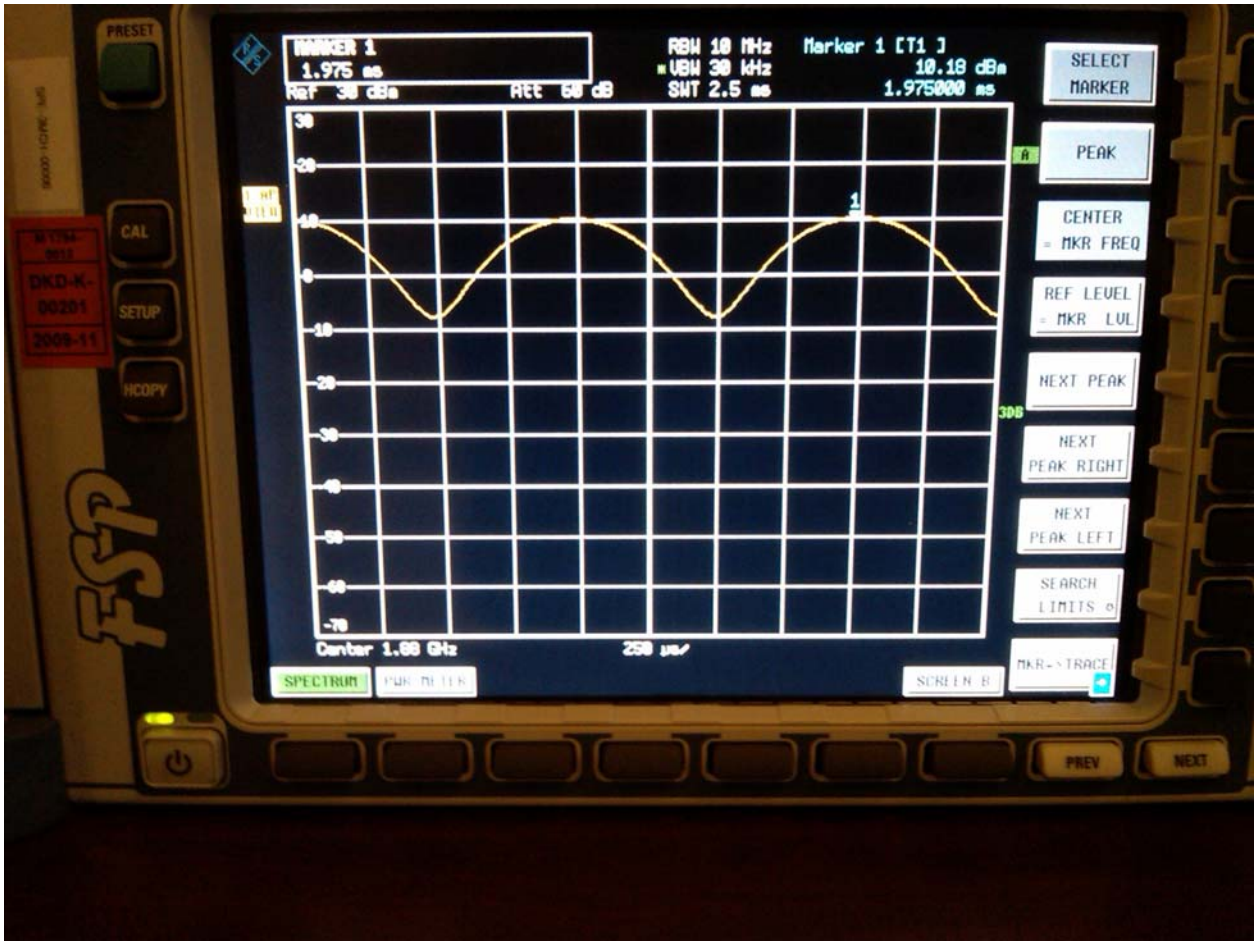
0 Hz Span 80% AM Plot (1880MHz)



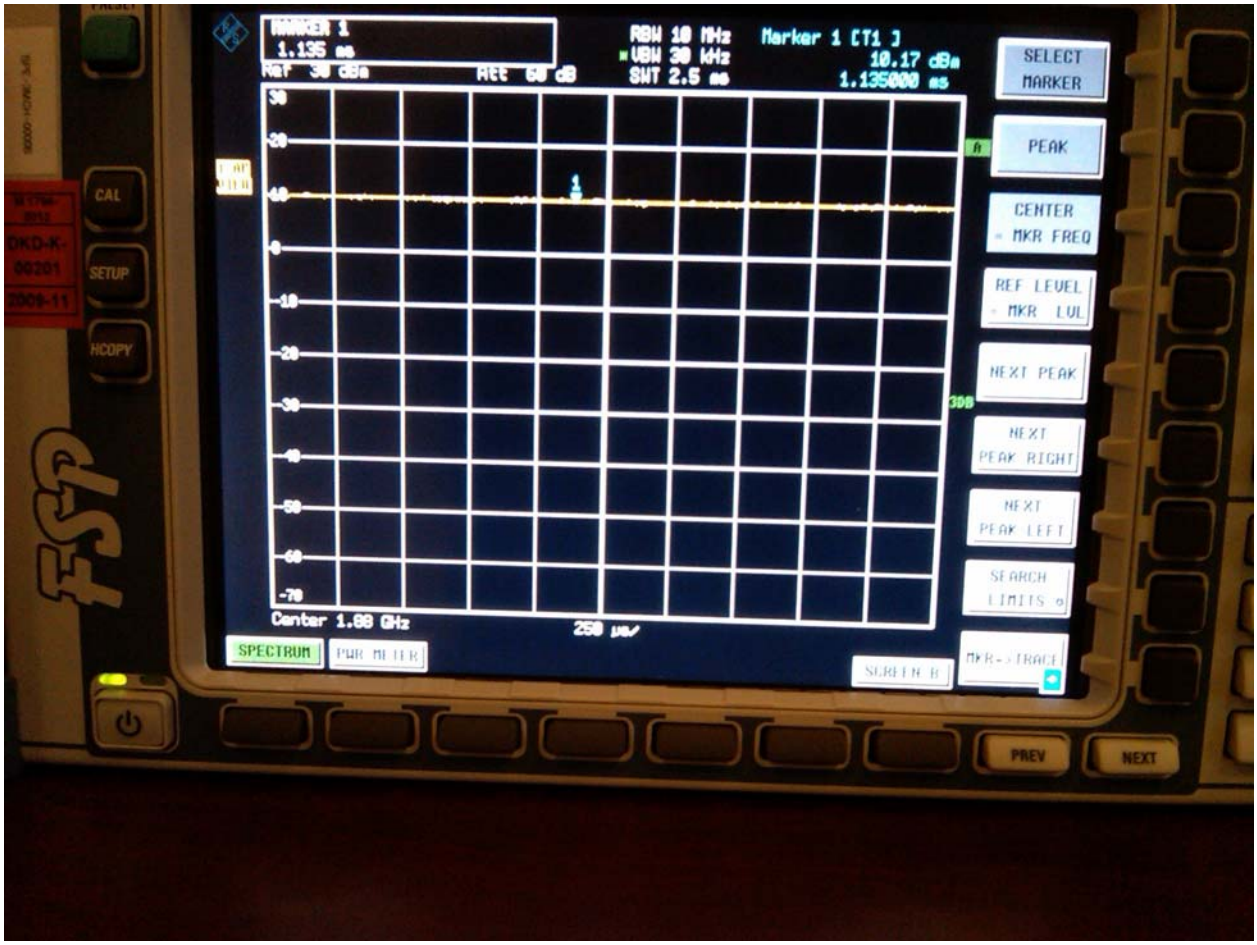
0 Hz Span GSM (1880MHz)



0 Hz Span CW Plot (1880MHz)



0 Hz Span 80% AM Plot (1880MHz)



0 Hz Span WCDMA (1880MHz)

A.2 Dipole validation and probe modulation factor plots

Date/Time: 3/10/2010 9:55:04 AM

File Name: HAC_E_Dipole_835MHz.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3;

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 107.1 V/m; Power Drift = -0.012 dB

Maximum value of Total (measured) = 167.7 V/m

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 168.3 V/m

Probe Modulation Factor = 1.00

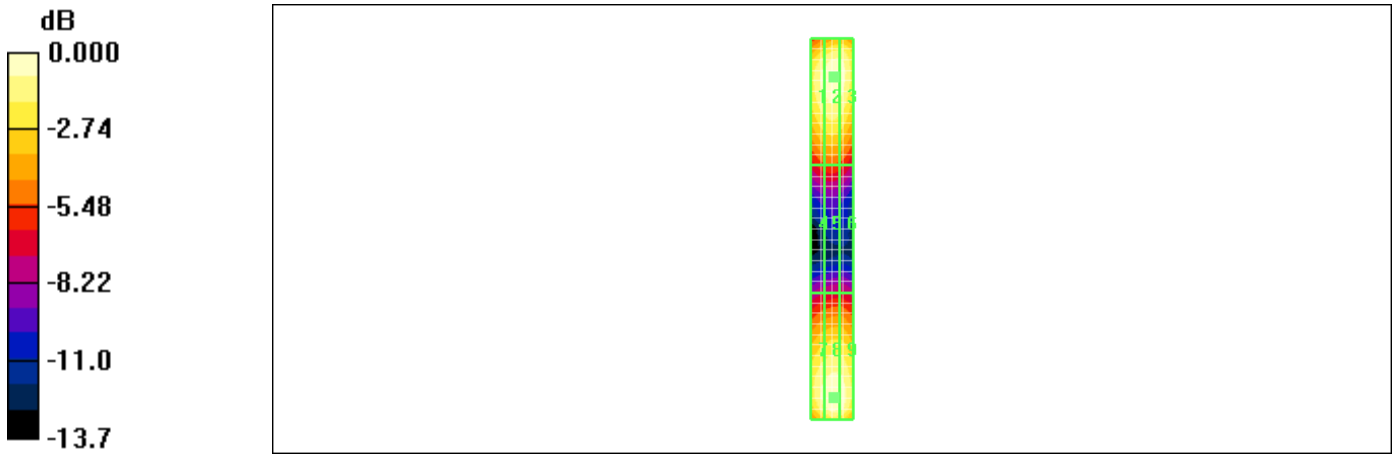
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 107.1 V/m; Power Drift = -0.012 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **159.1 M4**	Grid 2 **165.6 M4**	Grid 3 **163.3 M4**
Grid 4 **88.2 M4**	Grid 5 **89.9 M4**	Grid 6 **87.1 M4**
Grid 7 **159.8 M4**	Grid 8 **168.3 M4**	Grid 9 **165.7 M4**



0 dB = 168.3V/m

Date/Time: 3/10/2010 9:55:04 AM

File Name: HAC_E_Dipole_835MHz_CW_GSM_mod.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3;

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 107.1 V/m; Power Drift = -0.012 dB

Maximum value of Total (measured) = 167.7 V/m

E Scan - measurement distance from the probe sensor center to CD835

Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 168.3 V/m

Probe Modulation Factor = 1.00

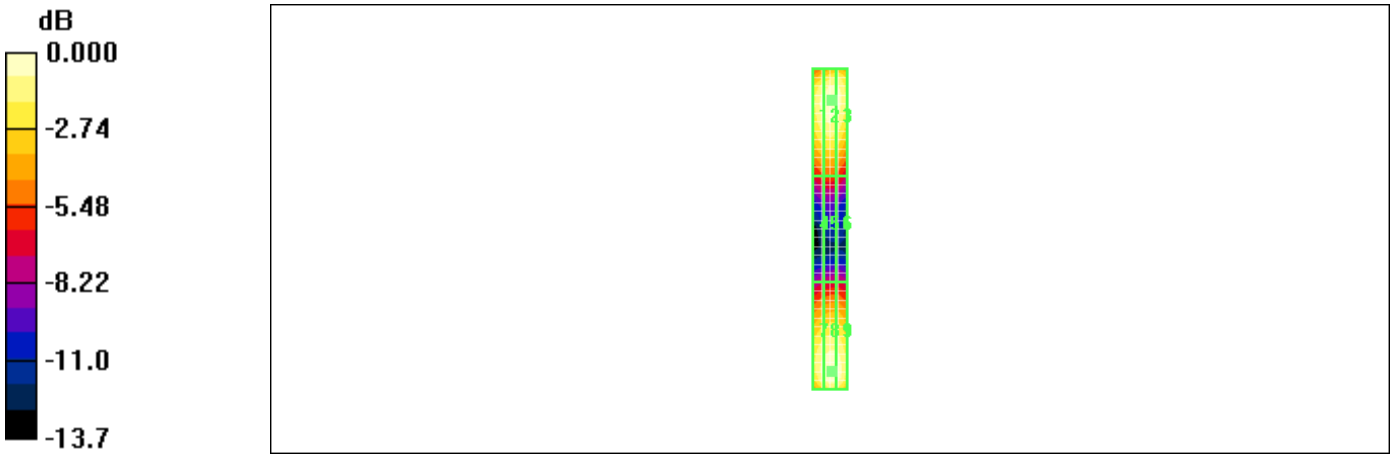
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 107.1 V/m; Power Drift = -0.012 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **159.1 M4**	Grid 2 **165.6 M4**	Grid 3 **163.3 M4**
Grid 4 **88.2 M4**	Grid 5 **89.9 M4**	Grid 6 **87.1 M4**
Grid 7 **159.8 M4**	Grid 8 **168.3 M4**	Grid 9 **165.7 M4**



0 dB = 168.3V/m

Date/Time: 3/10/2010 10:14:07 AM

File Name: HAC_E_Dipole_835MHz_AM80%_GSM_mod.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3;

Program Name: HAC RF E Dipole

Communication System: AM; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 66.9 V/m; Power Drift = 0.009 dB

Maximum value of Total (measured) = 103.4 V/m

E Scan - measurement distance from the probe sensor center to CD835

Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 103.9 V/m

Probe Modulation Factor = 1.00

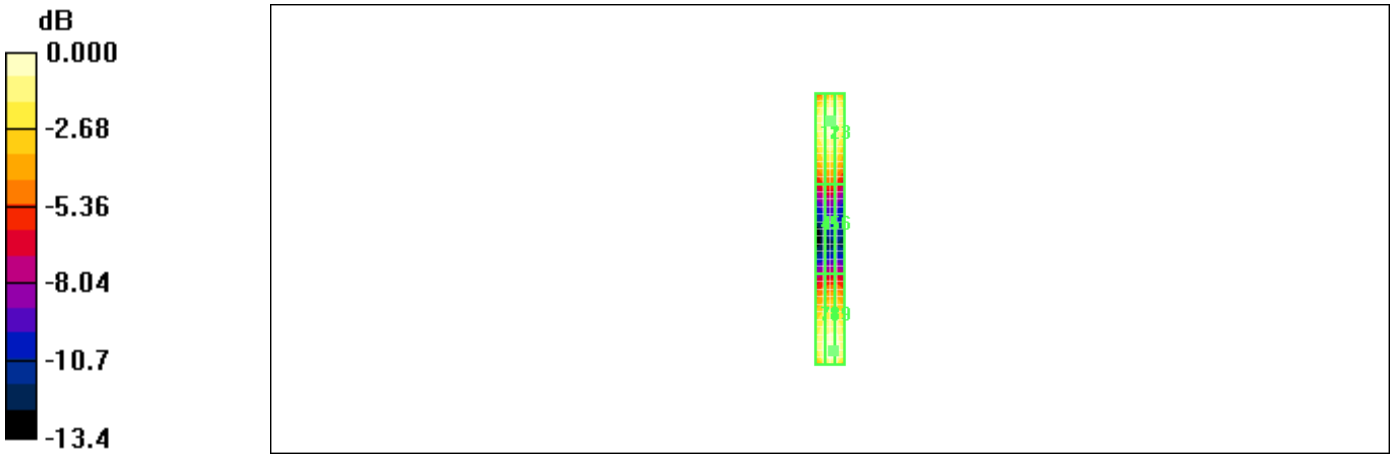
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 66.9 V/m; Power Drift = 0.009 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **98.5 M4**	Grid 2 **101.9 M4**	Grid 3 **100.5 M4**
Grid 4 **55.5 M4**	Grid 5 **56.6 M4**	Grid 6 **54.9 M4**
Grid 7 **98.9 M4**	Grid 8 **103.9 M4**	Grid 9 **102.8 M4**



0 dB = 103.9V/m

Date/Time: 3/10/2010 10:40:51 AM

File Name: HAC_E_Dipole_835MHz_GSM_mod.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3;

Program Name: HAC RF E Dipole

Communication System: GSM 850; Frequency: 835 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 36.8 V/m; Power Drift = 0.108 dB

Maximum value of Total (measured) = 59.0 V/m

E Scan - measurement distance from the probe sensor center to CD835

Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 59.2 V/m

Probe Modulation Factor = 1.00

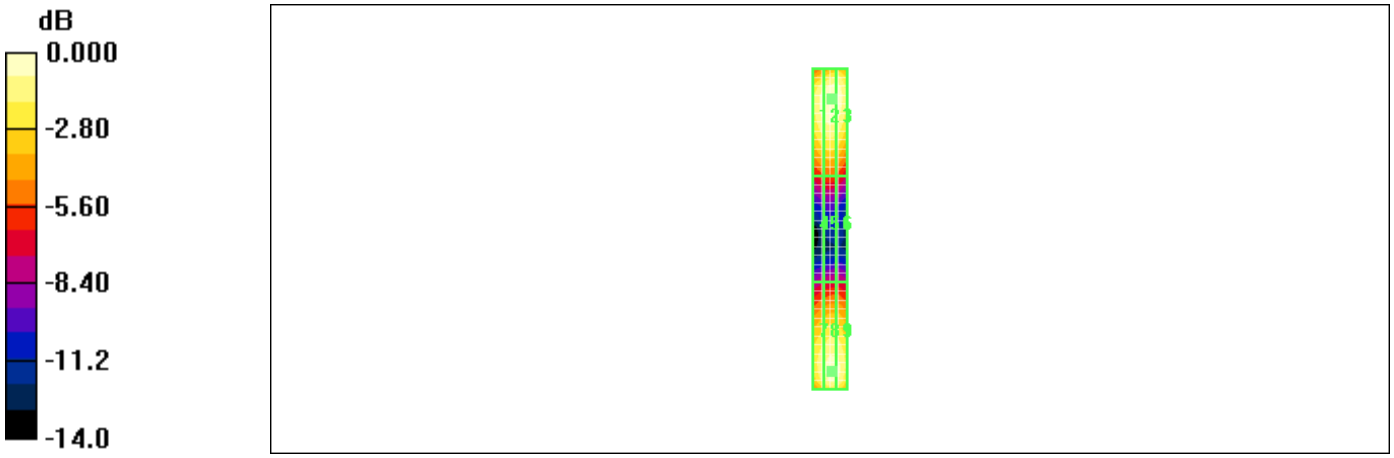
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 36.8 V/m; Power Drift = 0.108 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **56.7 M4**	Grid 2 **59.2 M4**	Grid 3 **58.6 M4**
Grid 4 **30.8 M4**	Grid 5 **31.5 M4**	Grid 6 **30.6 M4**
Grid 7 **53.6 M4**	Grid 8 **57.0 M4**	Grid 9 **56.3 M4**



0 dB = 59.2V/m

Date/Time: 3/10/2010 10:20:43 AM

File Name: HAC_E_Dipole_835MHz_CW_WCDMA_mod.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3;

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 39.3 V/m; Power Drift = -0.082 dB

Maximum value of Total (measured) = 60.7 V/m

E Scan - measurement distance from the probe sensor center to CD835

Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 60.9 V/m

Probe Modulation Factor = 1.00

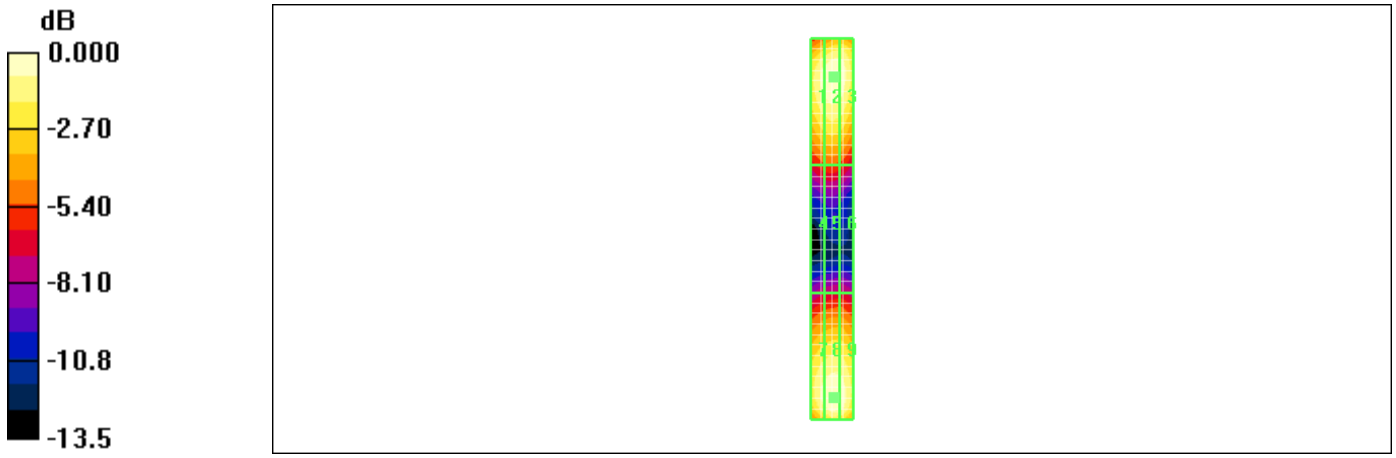
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 39.3 V/m; Power Drift = -0.082 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **57.8 M4**	Grid 2 **60.2 M4**	Grid 3 **59.5 M4**
Grid 4 **32.0 M4**	Grid 5 **32.8 M4**	Grid 6 **31.8 M4**
Grid 7 **58.0 M4**	Grid 8 **60.9 M4**	Grid 9 **60.1 M4**



0 dB = 60.9V/m

Date/Time: 3/10/2010 10:31:17 AM

File Name: HAC_E_Dipole_835MHz_AM80%_WCDMA.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3;

Program Name: HAC RF E Dipole

Communication System: AM; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 25.2 V/m; Power Drift = -0.266 dB

Maximum value of Total (measured) = 38.8 V/m

E Scan - measurement distance from the probe sensor center to CD835

Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 38.9 V/m

Probe Modulation Factor = 1.00

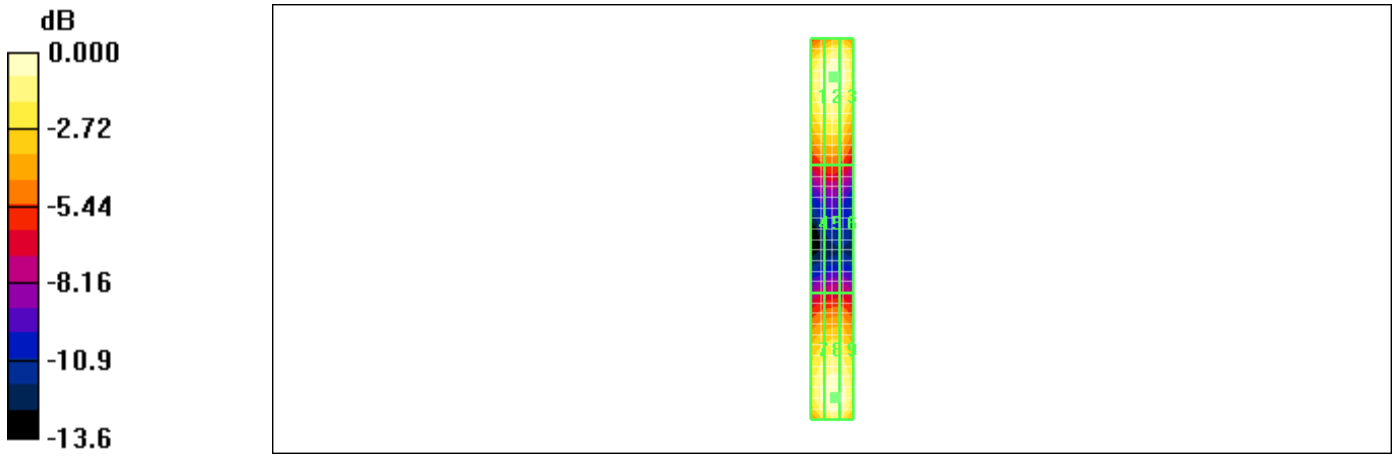
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 25.2 V/m; Power Drift = -0.266 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **36.9 M4**	Grid 2 **38.3 M4**	Grid 3 **37.9 M4**
Grid 4 **20.6 M4**	Grid 5 **21.0 M4**	Grid 6 **20.5 M4**
Grid 7 **37.0 M4**	Grid 8 **38.9 M4**	Grid 9 **38.4 M4**



0 dB = 38.9V/m

Date/Time: 3/10/2010 10:59:37 AM

File Name: HAC_E_Dipole_835MHz_WCDMA_mod.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3;

Program Name: HAC RF E Dipole

Communication System: WCDMA FDD V; Frequency: 836.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 38.9 V/m; Power Drift = -0.020 dB

Maximum value of Total (measured) = 62.4 V/m

E Scan - measurement distance from the probe sensor center to CD835

Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 62.6 V/m

Probe Modulation Factor = 1.00

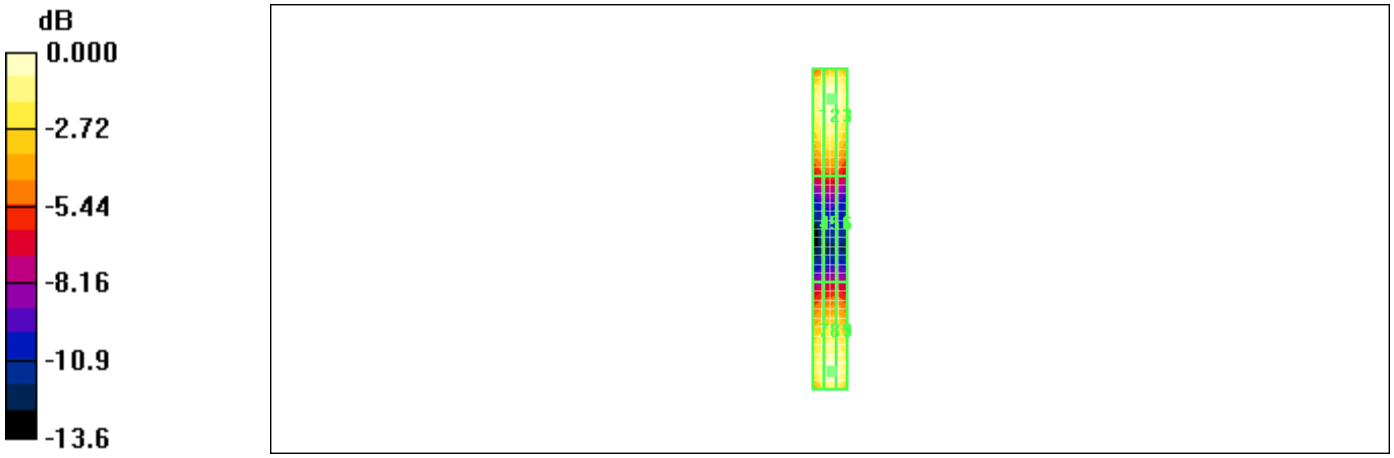
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 38.9 V/m; Power Drift = -0.020 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **60.1 M4**	Grid 2 **62.6 M4**	Grid 3 **61.7 M4**
Grid 4 **32.2 M4**	Grid 5 **32.9 M4**	Grid 6 **32.0 M4**
Grid 7 **57.8 M4**	Grid 8 **60.6 M4**	Grid 9 **59.7 M4**



0 dB = 62.6V/m

Date/Time: 3/10/2010 11:31:43 AM

File Name: HAC_E_Dipole_1880MHz.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3;

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 143.3 V/m; Power Drift = 0.033 dB

Maximum value of Total (measured) = 128.8 V/m

E Scan - measurement distance from the probe sensor center to CD1880

Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 129.1 V/m

Probe Modulation Factor = 1.00

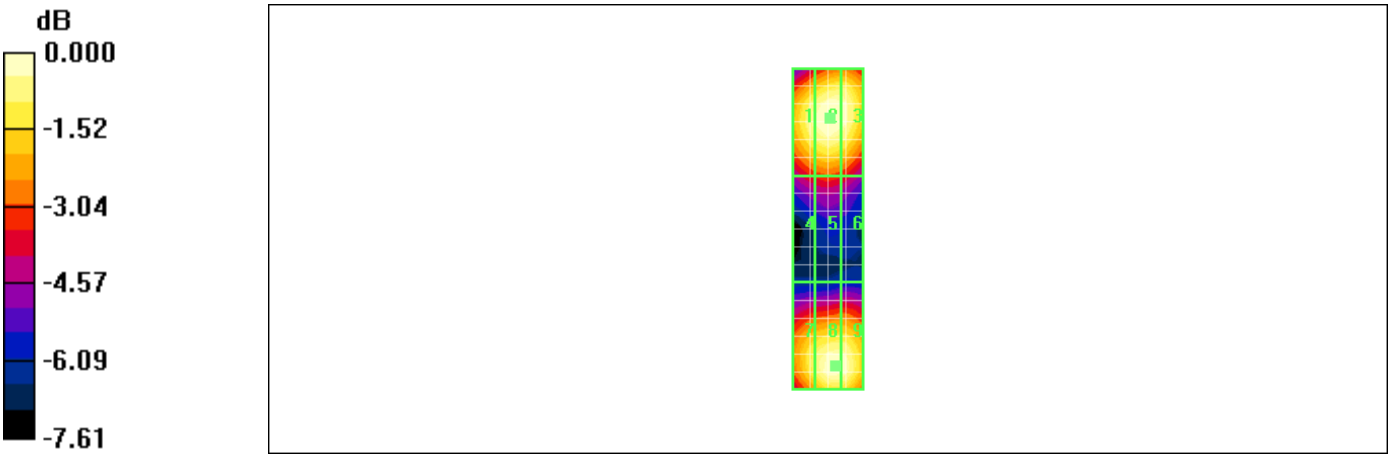
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 143.3 V/m; Power Drift = 0.033 dB

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **124.6 M2**	Grid 2 **129.1 M2**	Grid 3 **127.5 M2**
Grid 4 **88.2 M3**	Grid 5 **90.9 M3**	Grid 6 **88.0 M3**
Grid 7 **119.3 M2**	Grid 8 **128.7 M2**	Grid 9 **128.1 M2**



0 dB = 129.1V/m

Date/Time: 3/10/2010 11:44:25 AM

File Name: HAC_E_Dipole_1880MHz_CW_GSM_mod.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3;

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 108.7 V/m; Power Drift = 0.023 dB

Maximum value of Total (measured) = 97.3 V/m

E Scan - measurement distance from the probe sensor center to CD1880

Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 97.5 V/m

Probe Modulation Factor = 1.00

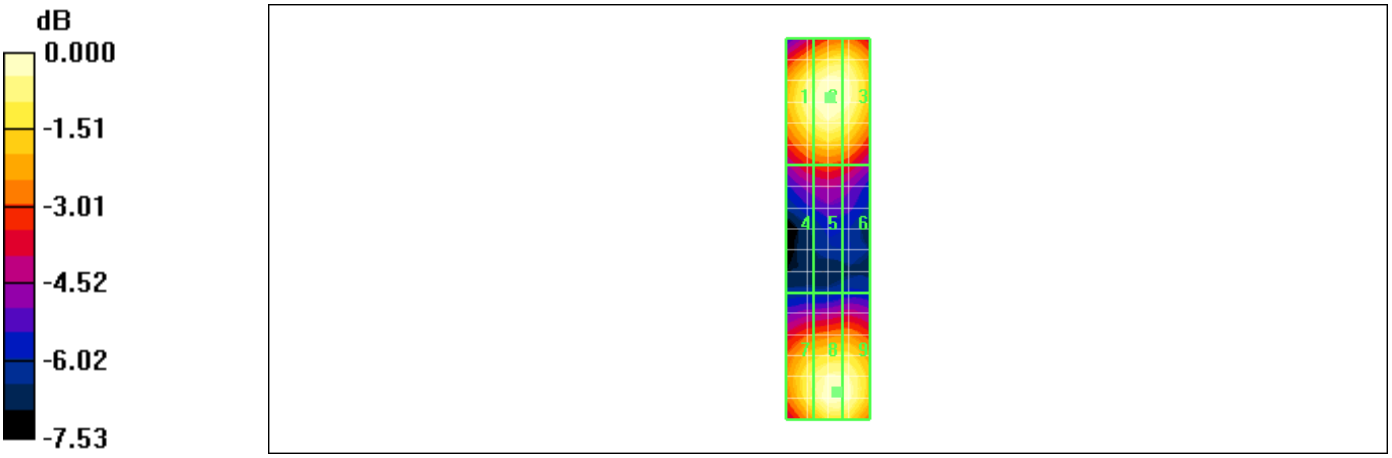
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 108.7 V/m; Power Drift = 0.023 dB

Hearing Aid Near-Field Category: M3 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **93.8 M3**	Grid 2 **97.5 M3**	Grid 3 **96.1 M3**
Grid 4 **66.5 M3**	Grid 5 **68.5 M3**	Grid 6 **66.5 M3**
Grid 7 **90.9 M3**	Grid 8 **97.5 M3**	Grid 9 **96.9 M3**



0 dB = 97.5V/m

Date/Time: 3/10/2010 11:50:57 AM

File Name: HAC_E_Dipole_1880MHz_AM80%_GSM.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3;

Program Name: HAC RF E Dipole

Communication System: AM; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 68.6 V/m; Power Drift = -0.011 dB

Maximum value of Total (measured) = 61.2 V/m

E Scan - measurement distance from the probe sensor center to CD1880

Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 61.9 V/m

Probe Modulation Factor = 1.00

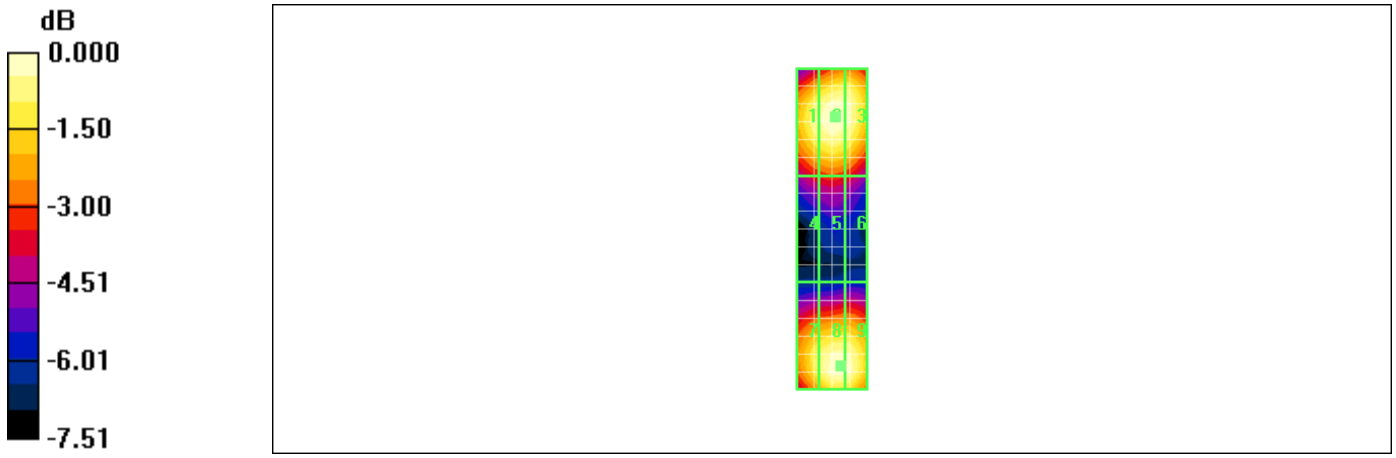
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 68.6 V/m; Power Drift = -0.011 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **59.4 M4**	Grid 2 **61.3 M4**	Grid 3 **60.9 M4**
Grid 4 **42.2 M4**	Grid 5 **43.5 M4**	Grid 6 **42.3 M4**
Grid 7 **57.2 M4**	Grid 8 **61.9 M4**	Grid 9 **61.6 M4**



0 dB = 61.9V/m

Date/Time: 3/10/2010 11:22:34 AM

File Name: HAC_E_Dipole_1880MHz_GSM_mod.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: GSM 1900; Frequency: 1880 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 17.9 V/m; Power Drift = 0.124 dB

Maximum value of Total (measured) = 35.9 V/m

H Scan - measurement distance from the probe sensor center to CD1880

Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 36.7 V/m

Probe Modulation Factor = 1.00

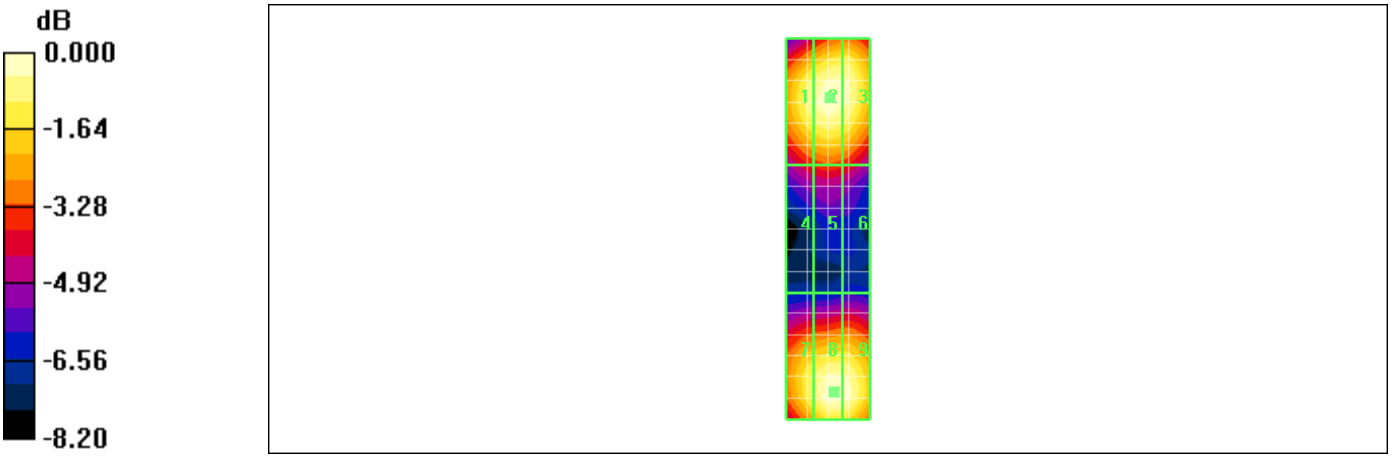
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 17.9 V/m; Power Drift = 0.124 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **34.6 M4**	Grid 2 **36.0 M4**	Grid 3 **35.6 M4**
Grid 4 **23.9 M4**	Grid 5 **24.9 M4**	Grid 6 **24.1 M4**
Grid 7 **33.6 M4**	Grid 8 **36.7 M4**	Grid 9 **36.4 M4**



0 dB = 36.7V/m

Date/Time: 3/10/2010 12:15:19 PM

File Name: HAC_E_Dipole_1880MHz_CW_WCDMA_mod.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3;

Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 47.6 V/m; Power Drift = 0.002 dB

Maximum value of Total (measured) = 42.3 V/m

E Scan - measurement distance from the probe sensor center to CD1880

Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 42.6 V/m

Probe Modulation Factor = 1.00

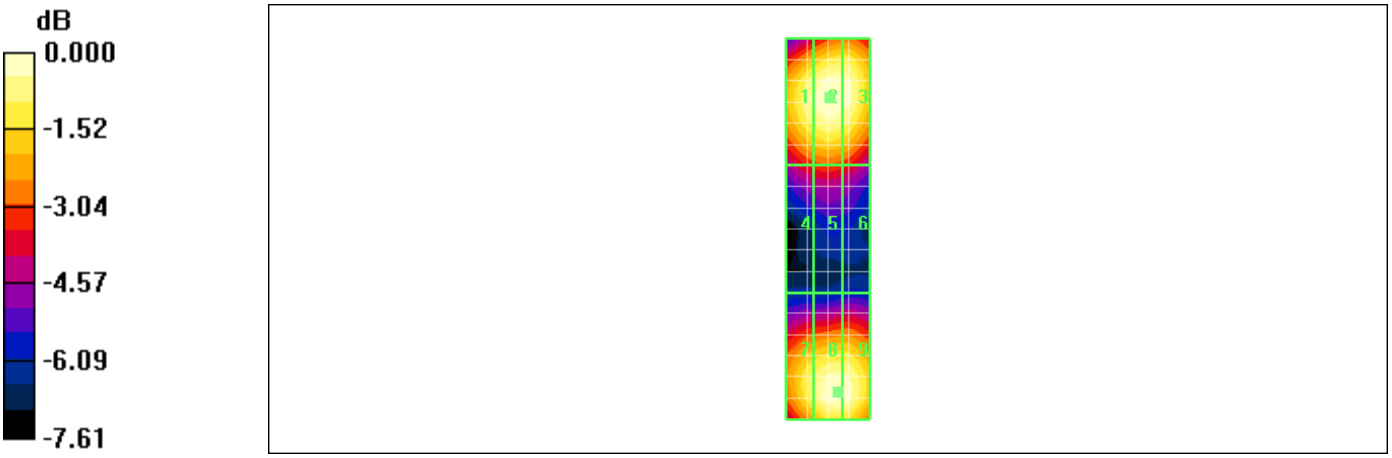
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 47.6 V/m; Power Drift = 0.002 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **40.9 M4**	Grid 2 **42.4 M4**	Grid 3 **42.0 M4**
Grid 4 **29.1 M4**	Grid 5 **30.0 M4**	Grid 6 **29.1 M4**
Grid 7 **39.4 M4**	Grid 8 **42.6 M4**	Grid 9 **42.4 M4**



0 dB = 42.6V/m

Date/Time: 3/10/2010 12:08:52 PM

File Name: HAC_E_Dipole_1880MHz_AM80%_WCDMA.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3;

Program Name: HAC RF E Dipole

Communication System: AM; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 30.4 V/m; Power Drift = 0.009 dB

Maximum value of Total (measured) = 27.1 V/m

E Scan - measurement distance from the probe sensor center to CD1880

Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 27.4 V/m

Probe Modulation Factor = 1.00

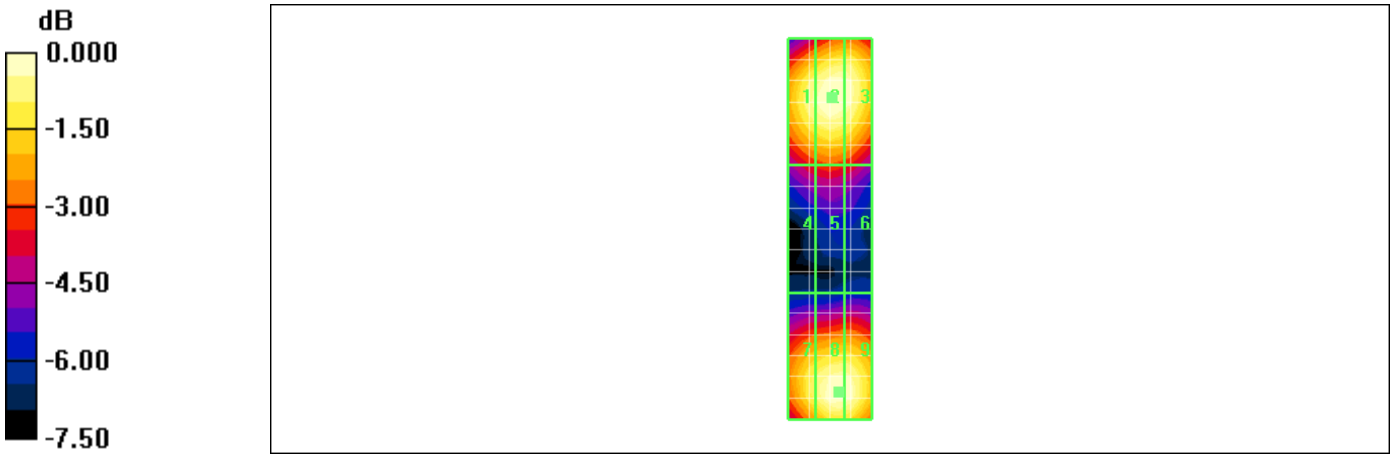
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 30.4 V/m; Power Drift = 0.009 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **26.2 M4**	Grid 2 **27.2 M4**	Grid 3 **26.9 M4**
Grid 4 **18.6 M4**	Grid 5 **19.2 M4**	Grid 6 **18.7 M4**
Grid 7 **25.3 M4**	Grid 8 **27.4 M4**	Grid 9 **27.2 M4**



0 dB = 27.4V/m

Date/Time: 3/10/2010 11:16:10 AM

File Name: HAC_E_Dipole_1880MHz_WCDMA_mod.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: WCDMA FDD II; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 23.2 V/m; Power Drift = -0.014 dB

Maximum value of Total (measured) = 46.1 V/m

H Scan - measurement distance from the probe sensor center to CD1880

Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 46.7 V/m

Probe Modulation Factor = 1.00

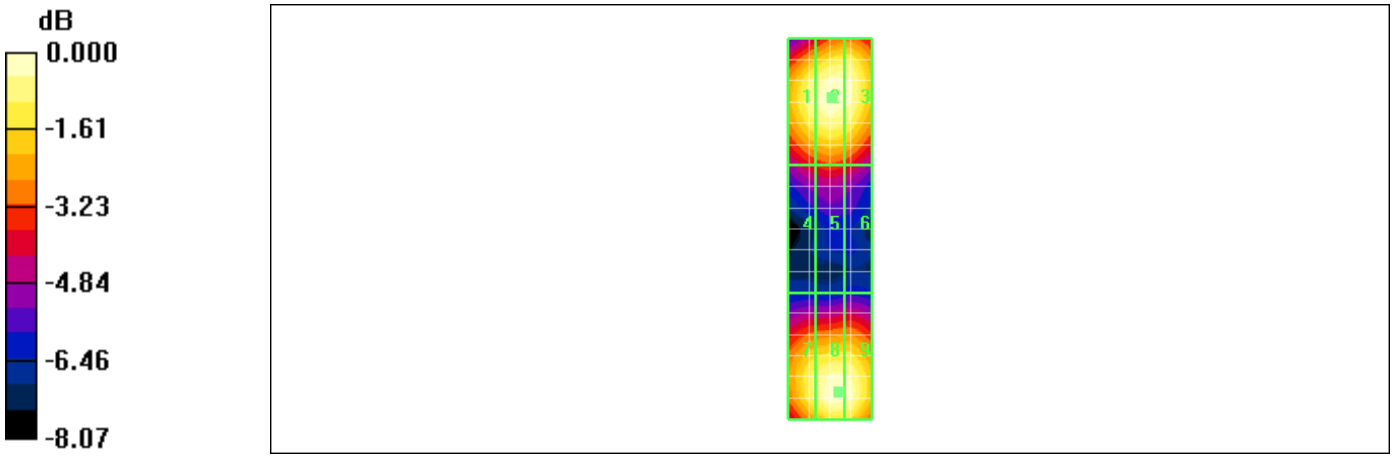
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 23.2 V/m; Power Drift = -0.014 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **44.3 M4**	Grid 2 **46.2 M4**	Grid 3 **45.7 M4**
Grid 4 **30.6 M4**	Grid 5 **31.7 M4**	Grid 6 **30.7 M4**
Grid 7 **43.4 M4**	Grid 8 **46.7 M4**	Grid 9 **46.4 M4**



0 dB = 46.7V/m

Date/Time: 3/10/2010 2:28:11 PM

File Name: HAC_H_Dipole_835MHz.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.510 A/m; Power Drift = 0.063 dB

Maximum value of Total (measured) = 0.482 A/m

H Scan - measurement distance from the probe sensor center to CD835

Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.483 A/m

Probe Modulation Factor = 1.00

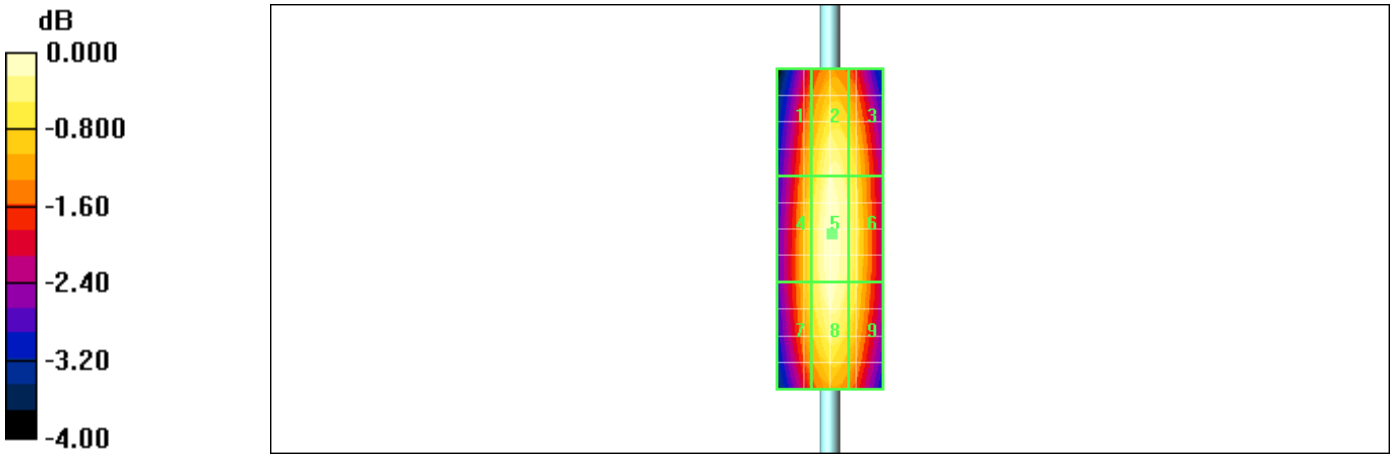
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.510 A/m; Power Drift = 0.063 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.441 M4**	Grid 2 **0.473 M4**	Grid 3 **0.460 M4**
Grid 4 **0.454 M4**	Grid 5 **0.483 M4**	Grid 6 **0.467 M4**
Grid 7 **0.452 M4**	Grid 8 **0.479 M4**	Grid 9 **0.463 M4**



0 dB = 0.483A/m

Date/Time: 3/10/2010 2:28:11 PM

File Name: HAC_H_Dipole_835MHz_CW_GSM_mod.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.510 A/m; Power Drift = 0.063 dB

Maximum value of Total (measured) = 0.482 A/m

H Scan - measurement distance from the probe sensor center to CD835

Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.483 A/m

Probe Modulation Factor = 1.00

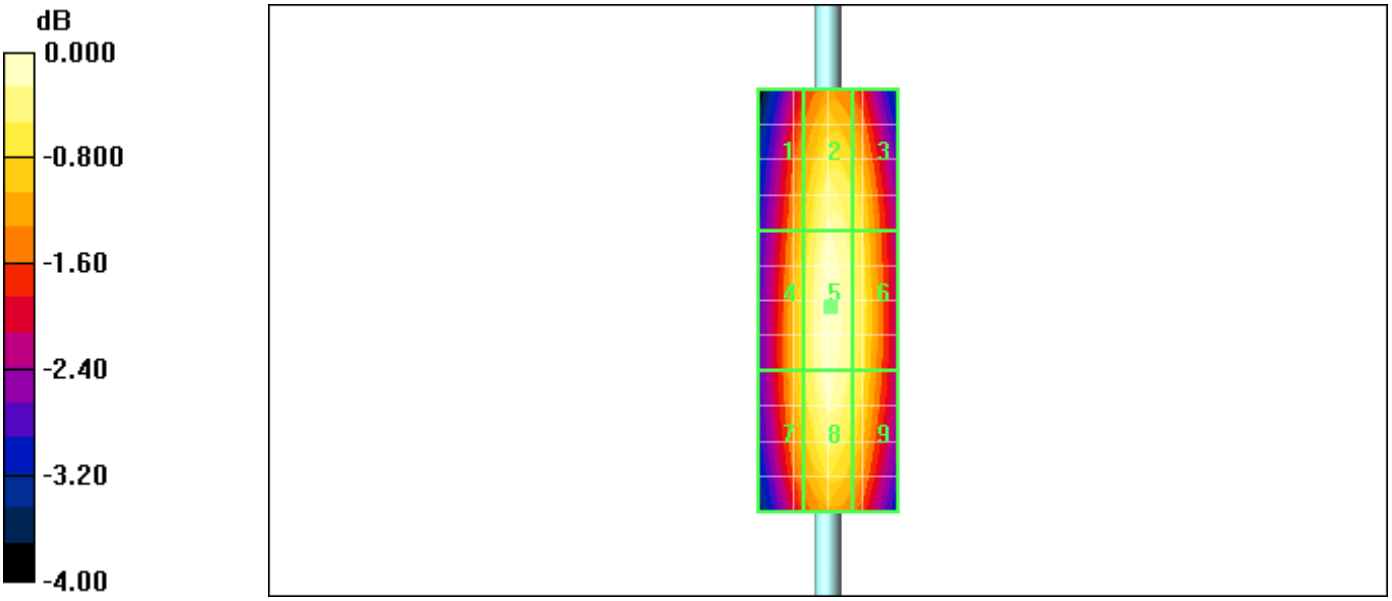
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.510 A/m; Power Drift = 0.063 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.441 M4**	Grid 2 **0.473 M4**	Grid 3 **0.460 M4**
Grid 4 **0.454 M4**	Grid 5 **0.483 M4**	Grid 6 **0.467 M4**
Grid 7 **0.452 M4**	Grid 8 **0.479 M4**	Grid 9 **0.463 M4**



0 dB = 0.483A/m

Date/Time: 3/10/2010 2:45:40 PM

File Name: HAC_H_Dipole_835MHz_AM80%_mod.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: AM 80%; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.328 A/m; Power Drift = 0.048 dB

Maximum value of Total (measured) = 0.308 A/m

H Scan - measurement distance from the probe sensor center to CD835

Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.309 A/m

Probe Modulation Factor = 1.00

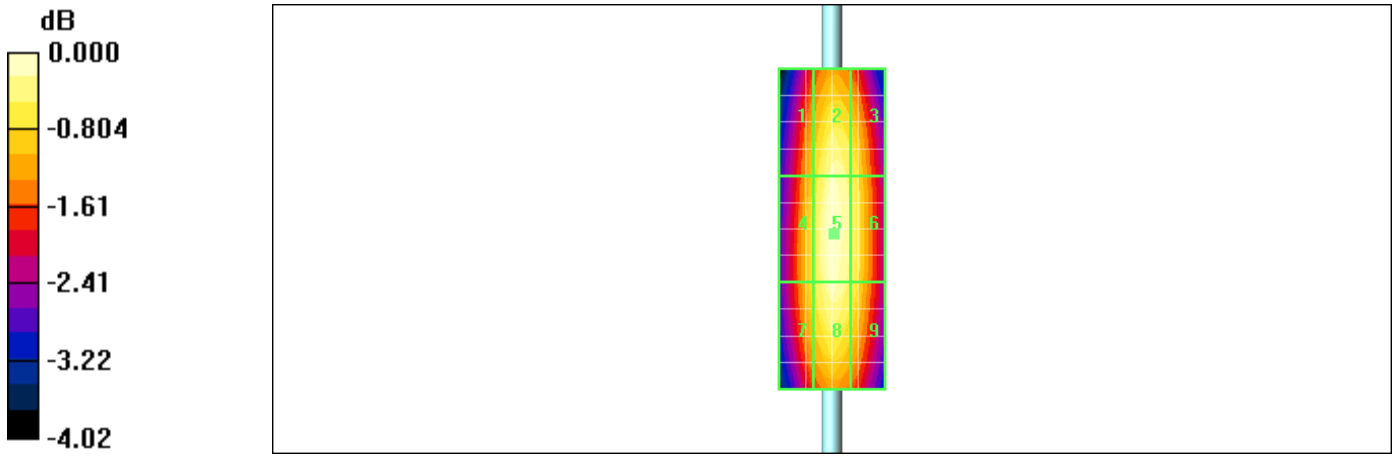
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.328 A/m; Power Drift = 0.048 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.283 M4**	Grid 2 **0.303 M4**	Grid 3 **0.295 M4**
Grid 4 **0.290 M4**	Grid 5 **0.309 M4**	Grid 6 **0.299 M4**
Grid 7 **0.289 M4**	Grid 8 **0.304 M4**	Grid 9 **0.295 M4**



0 dB = 0.309A/m

Date/Time: 3/10/2010 3:12:33 PM

File Name: HAC_H_Dipole_835MHz_GSM_mod.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: GSM 850; Frequency: 835 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.185 A/m; Power Drift = -0.105 dB

Maximum value of Total (measured) = 0.173 A/m

H Scan - measurement distance from the probe sensor center to CD835

Dipole = 10mm/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.173 A/m

Probe Modulation Factor = 1.00

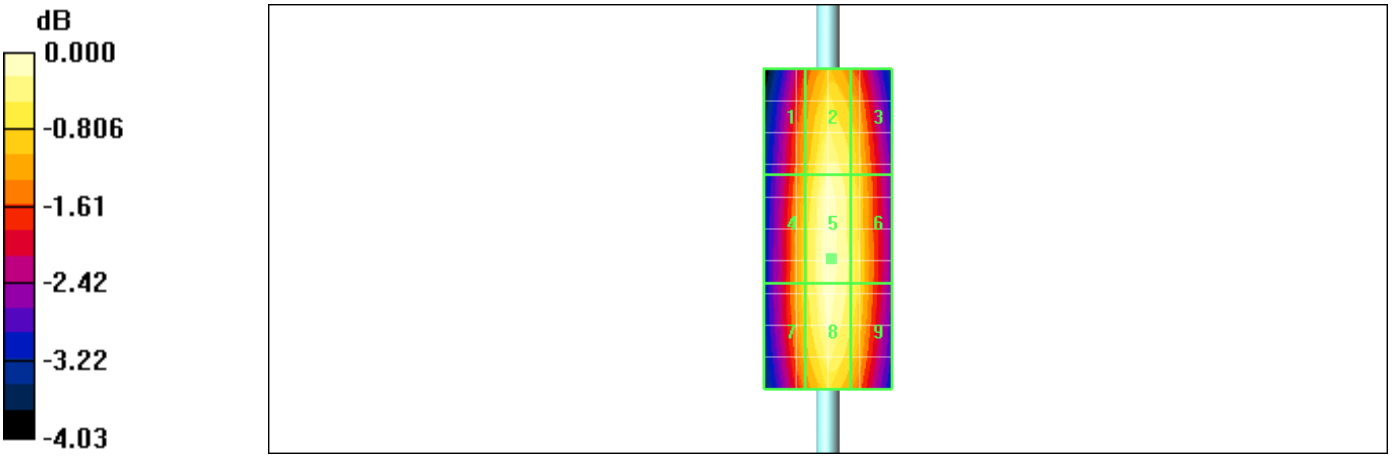
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.185 A/m; Power Drift = -0.105 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.155 M4**	Grid 2 **0.169 M4**	Grid 3 **0.163 M4**
Grid 4 **0.160 M4**	Grid 5 **0.173 M4**	Grid 6 **0.166 M4**
Grid 7 **0.161 M4**	Grid 8 **0.172 M4**	Grid 9 **0.166 M4**



0 dB = 0.173A/m

Date/Time: 3/10/2010 2:36:33 PM

File Name: HAC_H_Dipole_835MHz_CW_WCDMA_mod.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x13x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.188 A/m; Power Drift = -0.109 dB

Maximum value of Total (measured) = 0.174 A/m

H Scan - measurement distance from the probe sensor center to CD835

Dipole = 10mm/Hearing Aid Compatibility Test (41x121x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.174 A/m

Probe Modulation Factor = 1.00

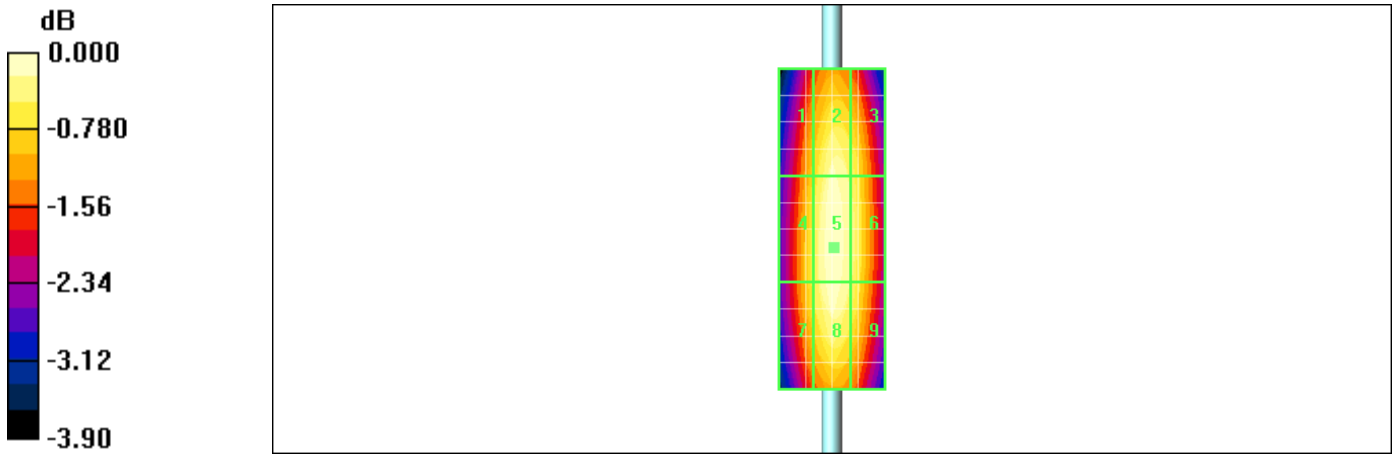
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.188 A/m; Power Drift = -0.109 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.160 M4**	Grid 2 **0.171 M4**	Grid 3 **0.167 M4**
Grid 4 **0.165 M4**	Grid 5 **0.174 M4**	Grid 6 **0.170 M4**
Grid 7 **0.165 M4**	Grid 8 **0.173 M4**	Grid 9 **0.168 M4**



0 dB = 0.174A/m

Date/Time: 3/10/2010 2:51:38 PM

File Name: HAC_H_Dipole_835MHz_AM80%_WCDMA_mod.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: AM 80%; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.119 A/m; Power Drift = 0.038 dB

Maximum value of Total (measured) = 0.112 A/m

H Scan - measurement distance from the probe sensor center to CD835

Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.112 A/m

Probe Modulation Factor = 1.00

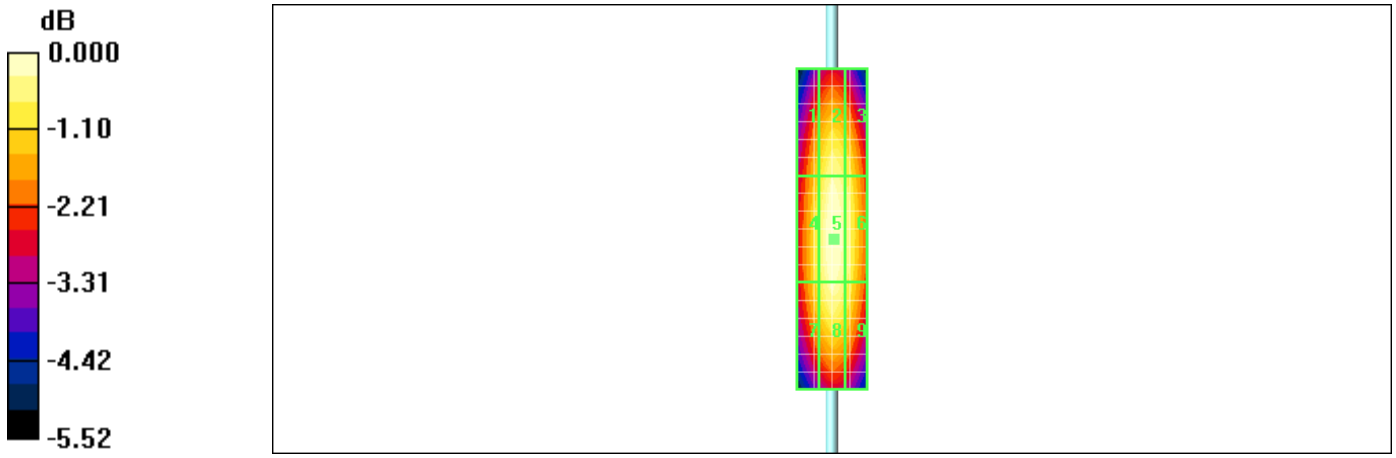
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.119 A/m; Power Drift = 0.038 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.100 M4**	Grid 2 **0.108 M4**	Grid 3 **0.105 M4**
Grid 4 **0.105 M4**	Grid 5 **0.112 M4**	Grid 6 **0.108 M4**
Grid 7 **0.103 M4**	Grid 8 **0.109 M4**	Grid 9 **0.106 M4**



0 dB = 0.112A/m

Date/Time: 3/10/2010 2:59:14 PM

File Name: HAC_H_Dipole_835MHz_WCDMA_mod.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: WCDMA FDD V; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.185 A/m; Power Drift = 0.001 dB

Maximum value of Total (measured) = 0.174 A/m

H Scan - measurement distance from the probe sensor center to CD835

Dipole = 10mm/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.174 A/m

Probe Modulation Factor = 1.00

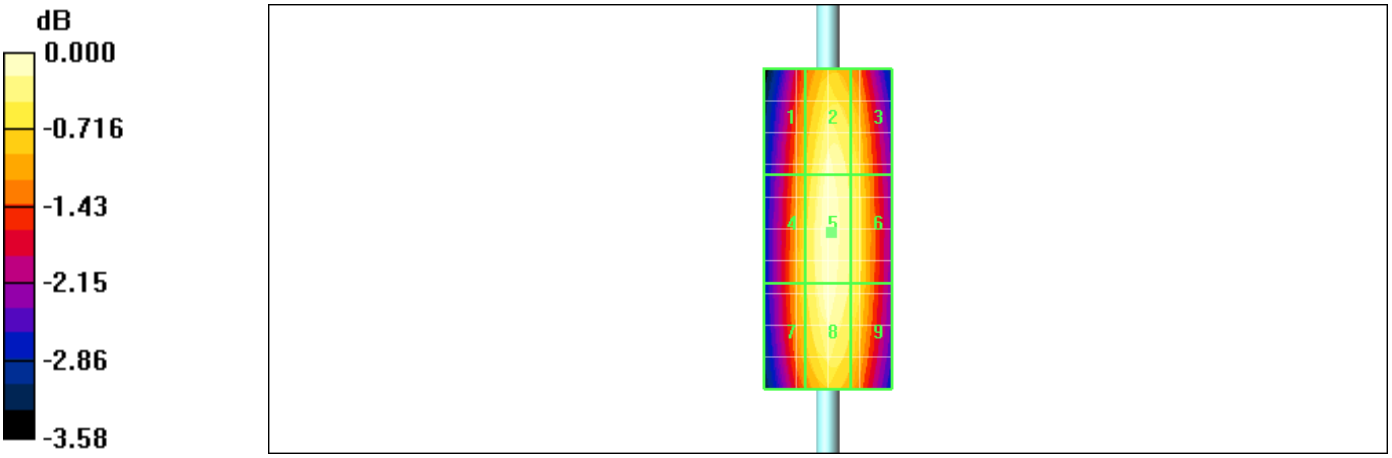
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.185 A/m; Power Drift = 0.001 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.160 M4**	Grid 2 **0.172 M4**	Grid 3 **0.168 M4**
Grid 4 **0.164 M4**	Grid 5 **0.174 M4**	Grid 6 **0.169 M4**
Grid 7 **0.164 M4**	Grid 8 **0.173 M4**	Grid 9 **0.168 M4**



0 dB = 0.174A/m

Date/Time: 3/10/2010 1:38:50 PM

File Name: HAC_H_Dipole_1880MHz.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.486 A/m; Power Drift = 0.008 dB

Maximum value of Total (measured) = 0.459 A/m

H Scan - measurement distance from the probe sensor center to CD1880

Dipole = 10mm/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.460 A/m

Probe Modulation Factor = 1.00

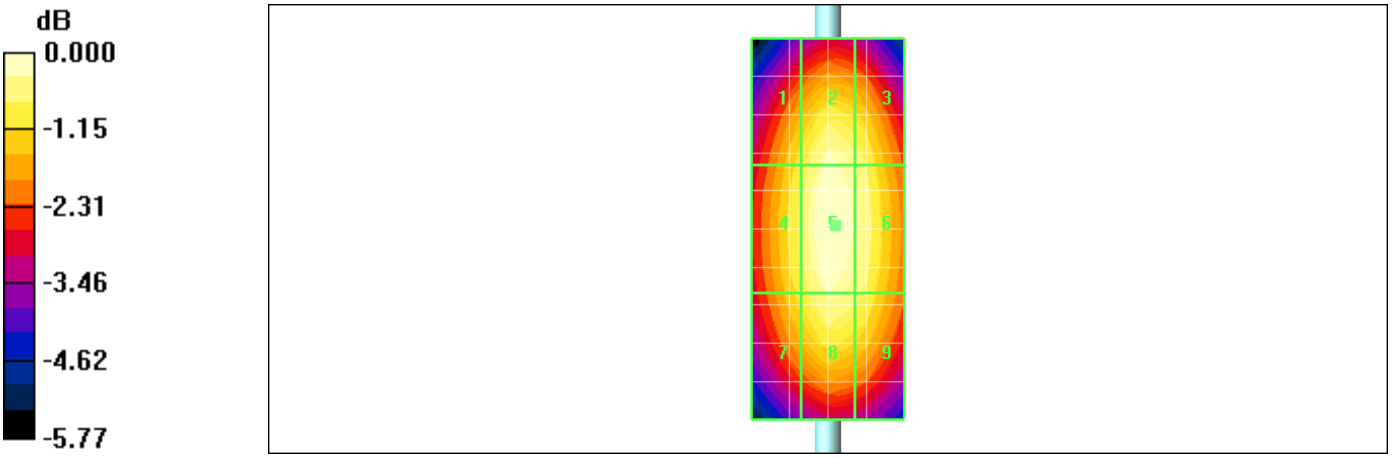
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.486 A/m; Power Drift = 0.008 dB

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.415 M2**	Grid 2 **0.448 M2**	Grid 3 **0.436 M2**
Grid 4 **0.429 M2**	Grid 5 **0.460 M2**	Grid 6 **0.447 M2**
Grid 7 **0.415 M2**	Grid 8 **0.443 M2**	Grid 9 **0.432 M2**



0 dB = 0.460A/m

Date/Time: 3/10/2010 1:48:16 PM

File Name: HAC_H_Dipole_1880MHz_CW_GSM_mod.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x10x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.369 A/m; Power Drift = -0.015 dB

Maximum value of Total (measured) = 0.347 A/m

H Scan - measurement distance from the probe sensor center to CD1880

Dipole = 10mm/Hearing Aid Compatibility Test (41x91x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.348 A/m

Probe Modulation Factor = 1.00

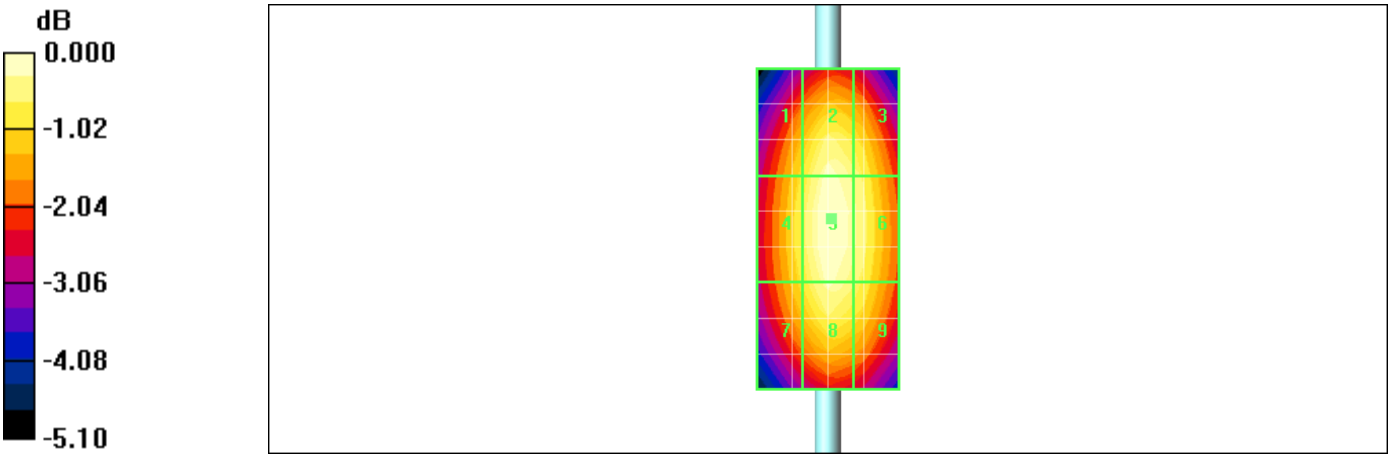
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.369 A/m; Power Drift = -0.015 dB

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.316 M3**	Grid 2 **0.341 M2**	Grid 3 **0.332 M3**
Grid 4 **0.324 M3**	Grid 5 **0.348 M2**	Grid 6 **0.338 M3**
Grid 7 **0.316 M3**	Grid 8 **0.339 M3**	Grid 9 **0.329 M3**



0 dB = 0.348A/m

Date/Time: 3/10/2010 1:55:22 PM

File Name: HAC_H_Dipole_1880MHz_AM80%_GSM_mod.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: AM 80%; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.240 A/m; Power Drift = -0.040 dB

Maximum value of Total (measured) = 0.227 A/m

H Scan - measurement distance from the probe sensor center to CD1880

Dipole = 10mm/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.227 A/m

Probe Modulation Factor = 1.00

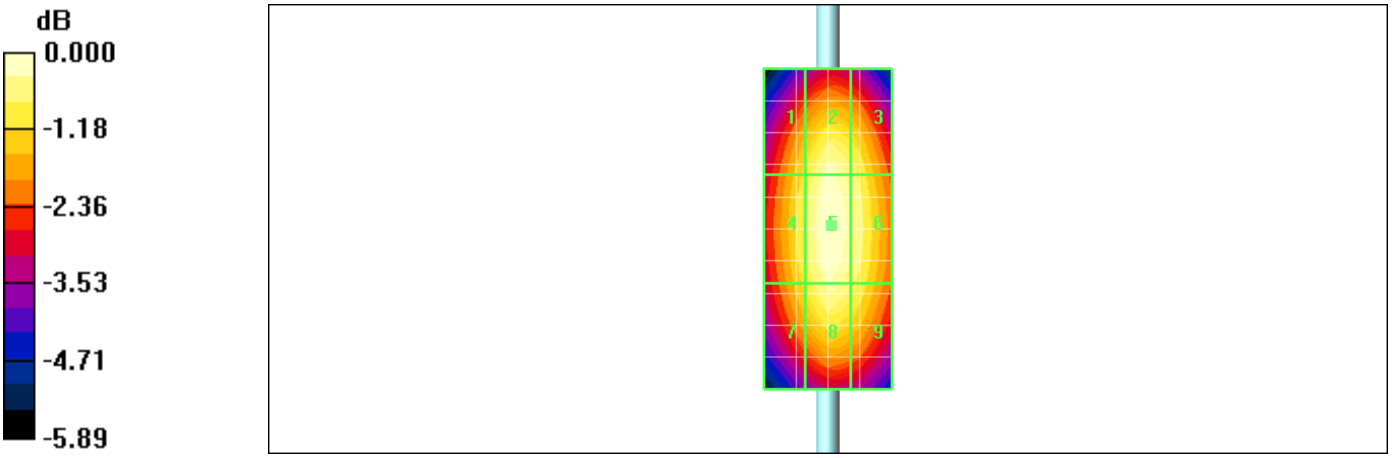
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.240 A/m; Power Drift = -0.040 dB

Hearing Aid Near-Field Category: M3 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.203 M3**	Grid 2 **0.221 M3**	Grid 3 **0.214 M3**
Grid 4 **0.210 M3**	Grid 5 **0.227 M3**	Grid 6 **0.219 M3**
Grid 7 **0.203 M3**	Grid 8 **0.219 M3**	Grid 9 **0.212 M3**



0 dB = 0.227A/m

Date/Time: 3/10/2010 2:03:45 PM

File Name: HAC_H_Dipole_1880MHz_GSM_mod.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: GSM 1900; Frequency: 1880 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.155 A/m; Power Drift = -0.086 dB

Maximum value of Total (measured) = 0.144 A/m

H Scan - measurement distance from the probe sensor center to CD1880

Dipole = 10mm/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.144 A/m

Probe Modulation Factor = 1.00

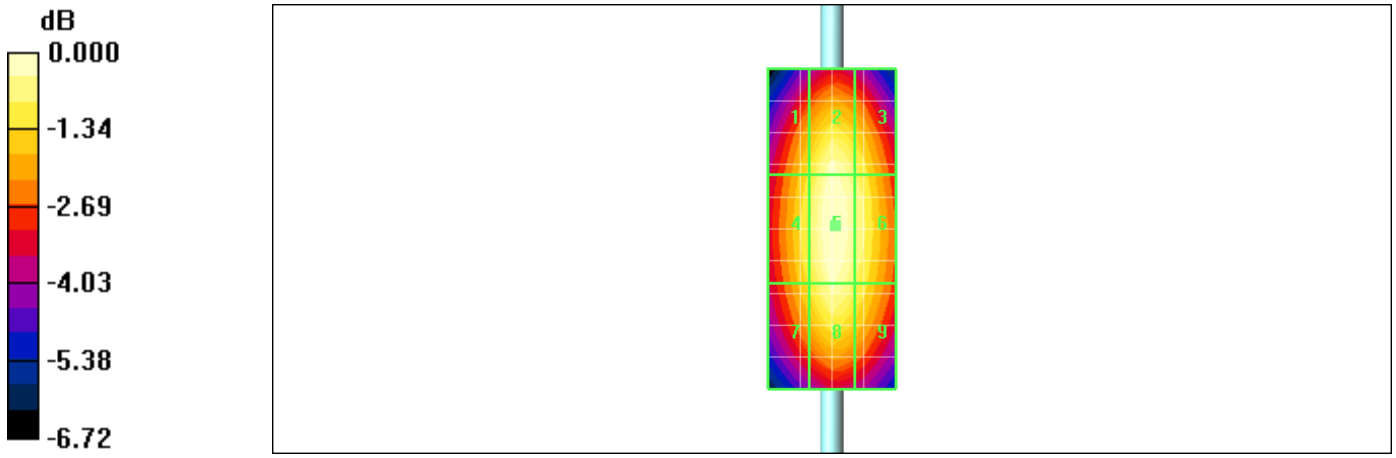
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.155 A/m; Power Drift = -0.086 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.127 M4**	Grid 2 **0.140 M3**	Grid 3 **0.133 M4**
Grid 4 **0.131 M4**	Grid 5 **0.144 M3**	Grid 6 **0.137 M4**
Grid 7 **0.126 M4**	Grid 8 **0.139 M4**	Grid 9 **0.132 M4**



0 dB = 0.144A/m

Date/Time: 3/10/2010 1:51:41 PM

File Name: HAC_H_Dipole_1880MHz_CW_WCDMA_mod.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.160 A/m; Power Drift = 0.011 dB

Maximum value of Total (measured) = 0.152 A/m

H Scan - measurement distance from the probe sensor center to CD1880

Dipole = 10mm/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.152 A/m

Probe Modulation Factor = 1.00

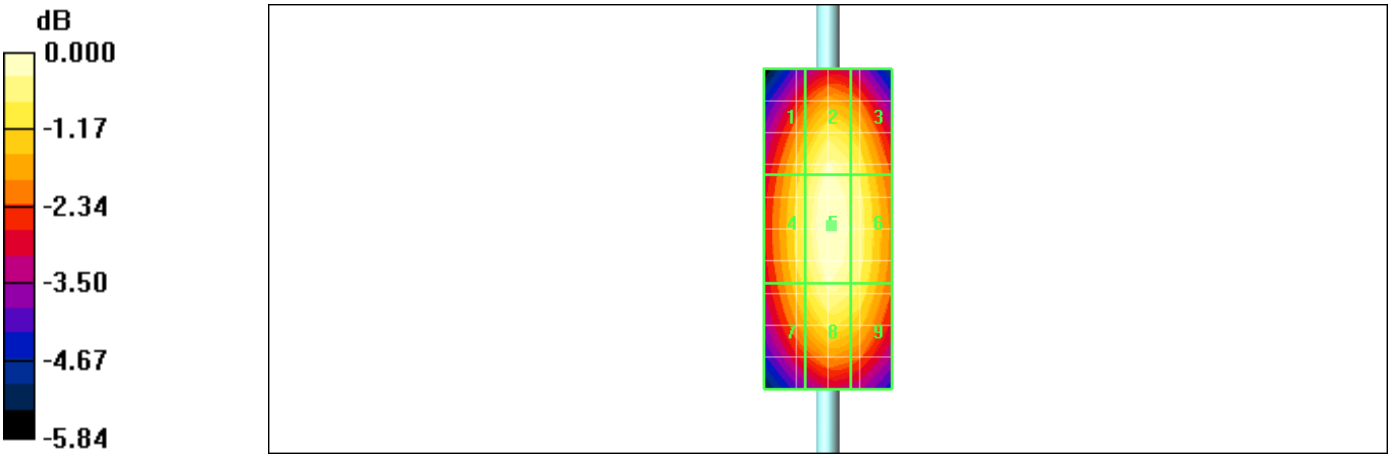
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.160 A/m; Power Drift = 0.011 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.137 M4**	Grid 2 **0.148 M4**	Grid 3 **0.143 M4**
Grid 4 **0.142 M4**	Grid 5 **0.152 M4**	Grid 6 **0.147 M4**
Grid 7 **0.137 M4**	Grid 8 **0.147 M4**	Grid 9 **0.143 M4**



0 dB = 0.152A/m

Date/Time: 3/10/2010 1:58:58 PM

File Name: HAC_H_Dipole_1880MHz_AM80%_WCDMA_mod.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: AM 80%; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.103 A/m; Power Drift = 0.066 dB

Maximum value of Total (measured) = 0.098 A/m

H Scan - measurement distance from the probe sensor center to CD1880

Dipole = 10mm/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.098 A/m

Probe Modulation Factor = 1.00

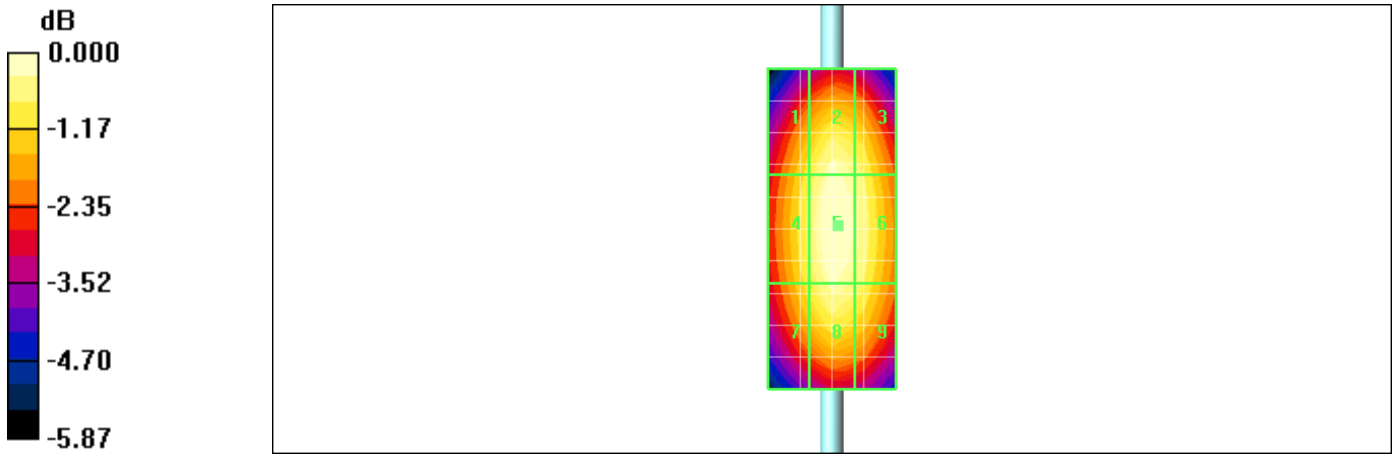
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.103 A/m; Power Drift = 0.066 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.088 M4**	Grid 2 **0.096 M4**	Grid 3 **0.093 M4**
Grid 4 **0.091 M4**	Grid 5 **0.098 M4**	Grid 6 **0.095 M4**
Grid 7 **0.089 M4**	Grid 8 **0.095 M4**	Grid 9 **0.092 M4**



0 dB = 0.098A/m

Date/Time: 3/10/2010 2:19:32 PM

File Name: HAC_H_Dipole_1880MHz_WCDMA_mod.da4

DUT: HAC Dipole 1880 MHz; Type: CD1880V3;

Program Name: HAC RF H3DV6 Dipole

Communication System: WCDMA FDD II; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (5x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.166 A/m; Power Drift = 0.009 dB

Maximum value of Total (measured) = 0.157 A/m

H Scan - measurement distance from the probe sensor center to CD1880

Dipole = 10mm/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.157 A/m

Probe Modulation Factor = 1.00

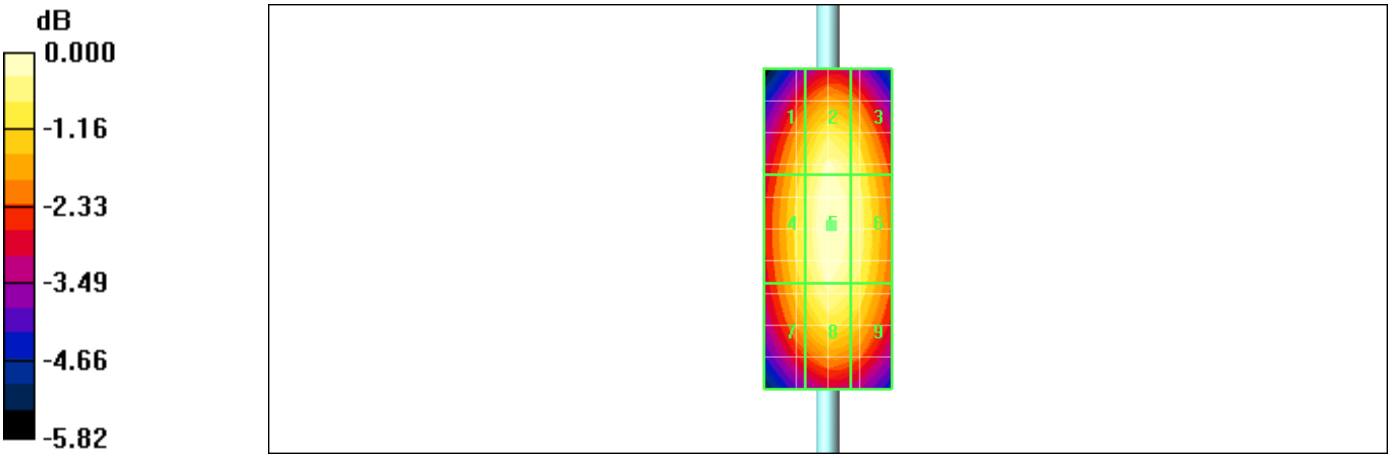
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.166 A/m; Power Drift = 0.009 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

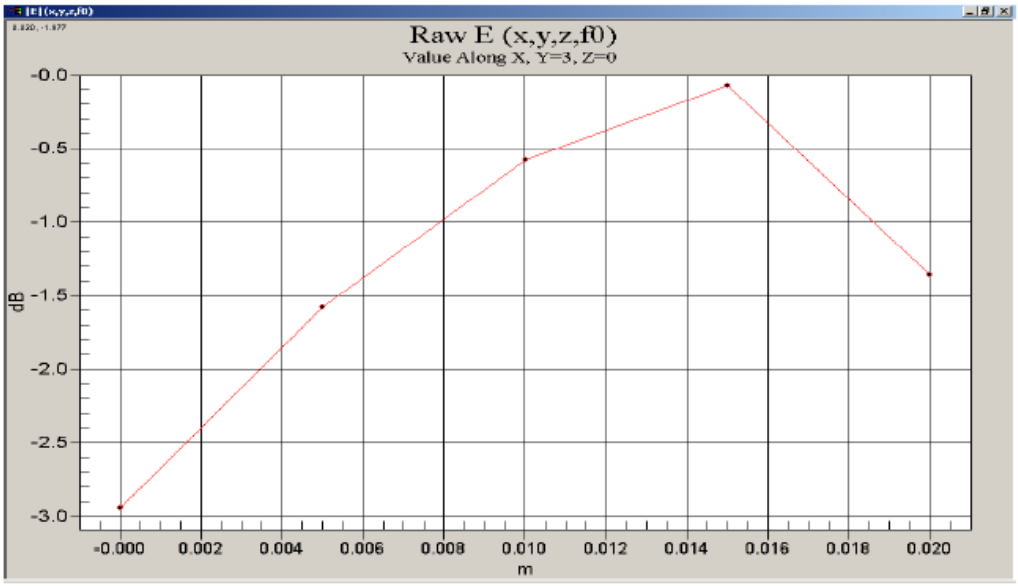
Grid 1 **0.142 M4**	Grid 2 **0.154 M4**	Grid 3 **0.149 M4**
Grid 4 **0.146 M4**	Grid 5 **0.157 M4**	Grid 6 **0.152 M4**
Grid 7 **0.142 M4**	Grid 8 **0.152 M4**	Grid 9 **0.147 M4**



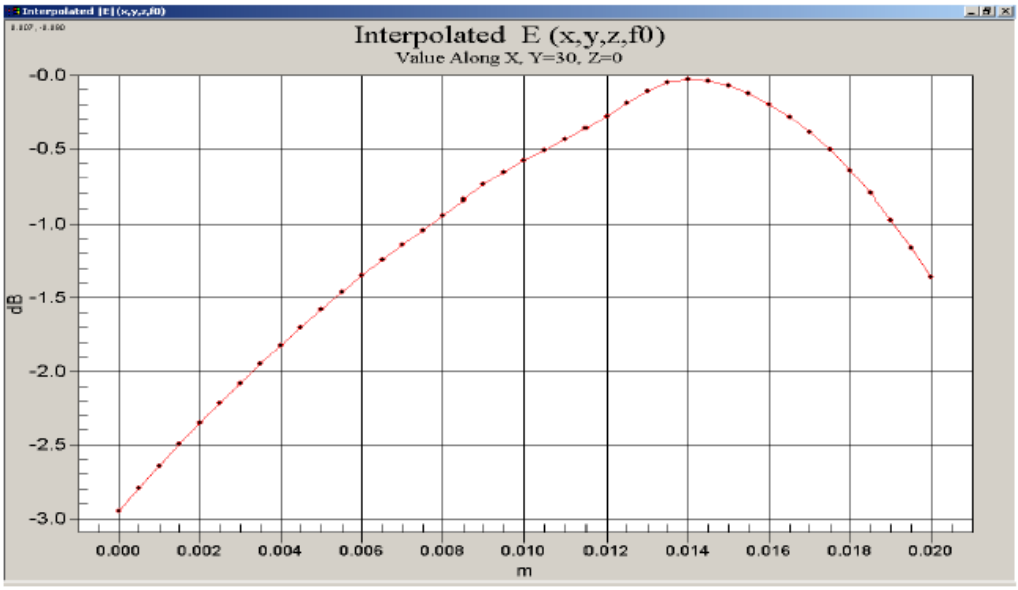
0 dB = 0.157A/m

Justification of Step Size and Interpolation

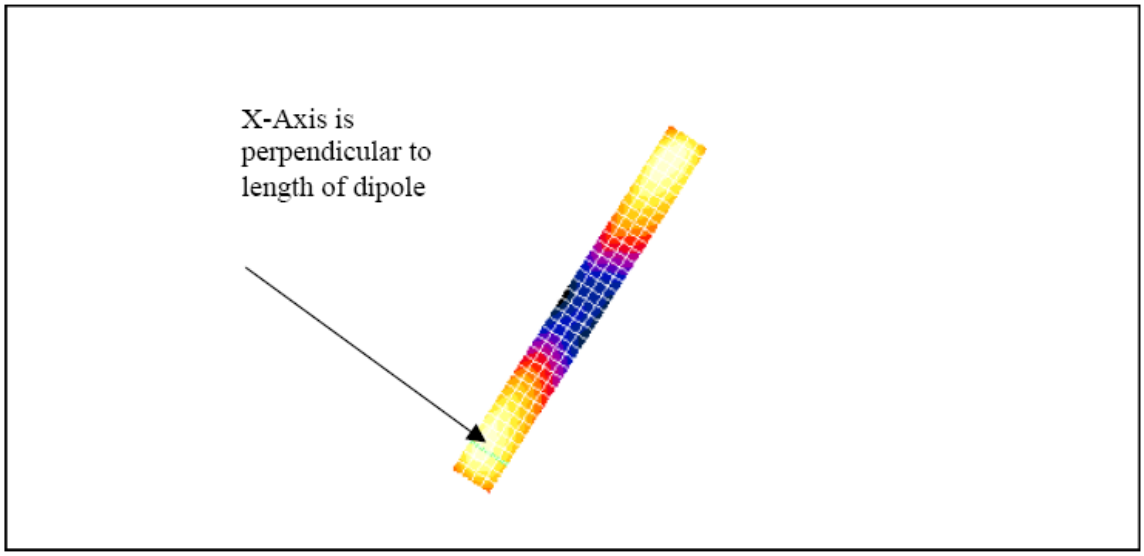
This section demonstrates that a 5mm step size with interpolation provides sufficient resolution for RF emissions measurements. The DASY 4 uses interpolation algorithms to derive 9 interpolated points between every measured point.



The figure above shows the raw measured field strength perpendicular to the length of the validation dipole. The TCB guidance slides require the 3dB width to be much larger than the step size. The width between -3dB points is > 21mm, at least 4 times the step size.



This figure shows the interpolated field strength perpendicular to the dipole. The interpolated points follow the raw points with no inconsistencies.



The green line in this figure shows the axis along which the points lie.

Comparison of 5mm and 2mm step sizes

An additional set of measurements was taken: dipole validations were performed using 5mm and 2mm step sizes. The delta between the two readings is insignificant for both field types (< 0.4% for E and 0% for H), demonstrating that 5mm is sufficient. The plots follow.

Date/Time: 14/07/2005 11:35:24 AM

Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1
Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3
Phantom section: H Device Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1):
Measurement grid: dx=5mm, dy=5mm
Maximum value of Total (measured) = 134.8 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1):
Measurement grid: dx=5mm, dy=5mm
Maximum value of Total field (slot averaged) = 131.0 V/m
Hearing Aid Near-Field Category: M2 (AWF 0 dB)

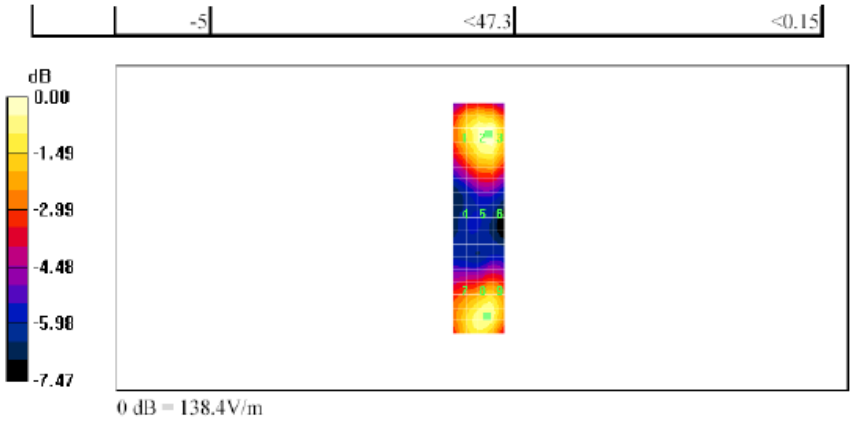
E in V/m (Time averaged)

Grid 1	Grid 2	Grid 3
123.2	**138.1**	**138.4**
Grid 4	Grid 5	Grid 6
80.9	**92.3**	**92.2**
Grid 7	Grid 8	Grid 9
119.8	**131.0**	**130.7**

E in V/m (Slot averaged)

Grid 1	Grid 2	Grid 3
123.2	**138.1**	**138.4**
Grid 4	Grid 5	Grid 6
80.9	**92.3**	**92.2**
Grid 7	Grid 8	Grid 9
119.8	**131.0**	**130.7**

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19



Date/Time: 14/07/2005 11:44:51 AM

Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_2mm step_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1
Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3
Phantom section: H Device Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1):
Measurement grid: dx=2mm, dy=2mm
Maximum value of Total (measured) = 138.0 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):
Measurement grid: dx=2mm, dy=2mm
Maximum value of Total field (slot averaged) = 131.2 V/m
Hearing Aid Near-Field Category: M2 (AWF 0 dB)

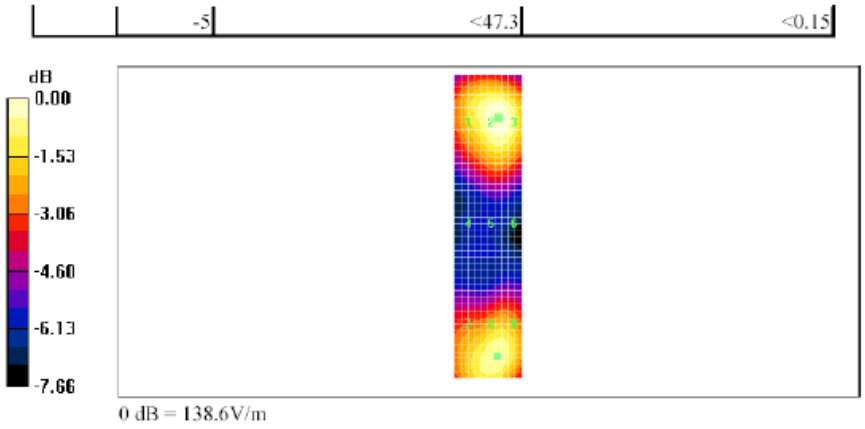
E in V/m (Time averaged)

Grid 1 **123.1**	Grid 2 **138.6**	Grid 3 **138.6**
Grid 4 **81.4**	Grid 5 **92.1**	Grid 6 **91.6**
Grid 7 **121.3**	Grid 8 **131.2**	Grid 9 **131.0**

E in V/m (Slot averaged)

Grid 1 **123.1**	Grid 2 **138.6**	Grid 3 **138.6**
Grid 4 **81.4**	Grid 5 **92.1**	Grid 6 **91.6**
Grid 7 **121.3**	Grid 8 **131.2**	Grid 9 **131.0**

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19



Date/Time: 14/07/2005 12:43:02 PM

Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_5 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1
Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3
Phantom section: H Dipole Section

DASY4 Configuration:
- Probe: H3DV6 - SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1):
Measurement grid: dx=5mm, dy=5mm
Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1):
Measurement grid: dx=5mm, dy=5mm
Maximum value of Total field (slot averaged) = 0.406 A/m
Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged)

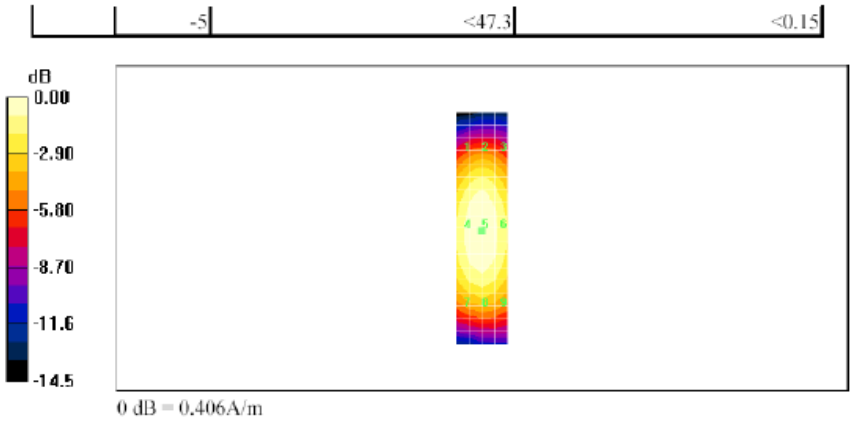
Grid 1	Grid 2	Grid 3
0.342	**0.359**	**0.344**
Grid 4	Grid 5	Grid 6
0.389	**0.406**	**0.389**
Grid 7	Grid 8	Grid 9
0.363	**0.378**	**0.363**

H in A/m (Slot averaged)

Grid 1	Grid 2	Grid 3
0.342	**0.359**	**0.344**
Grid 4	Grid 5	Grid 6
0.389	**0.406**	**0.389**
Grid 7	Grid 8	Grid 9
0.363	**0.378**	**0.363**

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

Date/Time: 14/07/2005 12:43:02 PM



0 dB = 0.406A/m

Date/Time: 14/07/2005 12:53:40 PM

Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_2 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1
Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3
Phantom section: H Dipole Section

DASY4 Configuration:
- Probe: H3DV6 - SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1):
Measurement grid: dx=2mm, dy=2mm
Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):
Measurement grid: dx=2mm, dy=2mm
Maximum value of Total field (slot averaged) = 0.406 A/m
Hearing Aid Near-Field Category: M2 (AWF 0 dB)

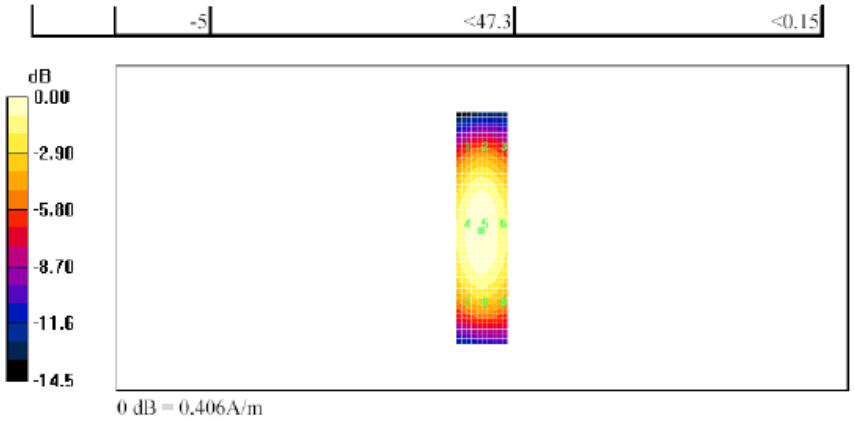
H in A/m (Time averaged)

Grid 1 **0.347**	Grid 2 **0.361**	Grid 3 **0.348**
Grid 4 **0.394**	Grid 5 **0.406**	Grid 6 **0.391**
Grid 7 **0.367**	Grid 8 **0.380**	Grid 9 **0.365**

H in A/m (Slot averaged)

Grid 1 **0.347**	Grid 2 **0.361**	Grid 3 **0.348**
Grid 4 **0.394**	Grid 5 **0.406**	Grid 6 **0.391**
Grid 7 **0.367**	Grid 8 **0.380**	Grid 9 **0.365**

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19



Date/Time: 3/10/2010 5:00:00 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_GSM_850_low chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 824.2 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 69.2 V/m; Power Drift = 0.084 dB

Maximum value of Total (measured) = 57.0 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 161.8 V/m

Probe Modulation Factor = 2.84

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 69.2 V/m; Power Drift = 0.084 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **138.9 M4**	Grid 2 **156.2 M3**	Grid 3 **154.7 M3**
Grid 4 **143.3 M4**	Grid 5 **161.8 M3**	Grid 6 **160.0 M3**
Grid 7 **141.5 M4**	Grid 8 **160.3 M3**	Grid 9 **158.4 M3**

0 dB = 161.8V/m

Date/Time: 3/10/2010 5:10:47 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_GSM_850_mid chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 836.8 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 73.5 V/m; Power Drift = 0.041 dB

Maximum value of Total (measured) = 61.4 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 174.4 V/m

Probe Modulation Factor = 2.84

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 73.5 V/m; Power Drift = 0.041 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **140.8 M4**	Grid 2 **165.8 M3**	Grid 3 **165.2 M3**
Grid 4 **148.6 M4**	Grid 5 **174.4 M3**	Grid 6 **172.4 M3**
Grid 7 **151.9 M3**	Grid 8 **172.9 M3**	Grid 9 **171.9 M3**

0 dB = 174.4V/m

Date/Time: 3/10/2010 5:18:45 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_GSM_850_high chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 848.8 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 70.0 V/m; Power Drift = -0.004 dB

Maximum value of Total (measured) = 57.8 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 164.2 V/m

Probe Modulation Factor = 2.84

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 70.0 V/m; Power Drift = -0.004 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **136.3 M4**	Grid 2 **158.6 M3**	Grid 3 **158.0 M3**
Grid 4 **140.2 M4**	Grid 5 **164.2 M3**	Grid 6 **163.3 M3**
Grid 7 **138.4 M4**	Grid 8 **162.5 M3**	Grid 9 **160.9 M3**

0 dB = 164.2V/m

Date/Time: 3/10/2010 5:42:59 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_GSM_850_mid chan_Telecoil.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF ER3D Device

Communication System: GSM 850; Frequency: 836.8 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 74.1 V/m; Power Drift = -0.192 dB

Maximum value of Total (measured) = 60.8 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 171.5 V/m

Probe Modulation Factor = 2.84

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 74.1 V/m; Power Drift = -0.192 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **135.5 M4**	Grid 2 **158.6 M3**	Grid 3 **158.6 M3**
Grid 4 **143.5 M4**	Grid 5 **171.5 M3**	Grid 6 **171.8 M3**
Grid 7 **144.4 M4**	Grid 8 **172.9 M3**	Grid 9 **173.1 M3**

0 dB = 173.1V/m

Date/Time: 3/10/2010 8:11:32 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_UMTS_band_V_low chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF ER3D Device

Communication System: WCDMA FDD V; Frequency: 826.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 65.0 V/m; Power Drift = 0.002 dB

Maximum value of Total (measured) = 53.4 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 51.8 V/m

Probe Modulation Factor = 0.970

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 65.0 V/m; Power Drift = 0.002 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **43.3 M4**	Grid 2 **49.5 M4**	Grid 3 **49.2 M4**
Grid 4 **45.3 M4**	Grid 5 **51.8 M4**	Grid 6 **51.3 M4**
Grid 7 **45.8 M4**	Grid 8 **51.5 M4**	Grid 9 **51.0 M4**

0 dB = 51.8V/m

Date/Time: 3/10/2010 8:46:16 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_UMTS_band_V_mid chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF ER3D Device

Communication System: WCDMA FDD V; Frequency: 836.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 67.9 V/m; Power Drift = 0.018 dB

Maximum value of Total (measured) = 55.9 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 54.3 V/m

Probe Modulation Factor = 0.970

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 67.9 V/m; Power Drift = 0.018 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **44.3 M4**	Grid 2 **51.5 M4**	Grid 3 **51.4 M4**
Grid 4 **46.6 M4**	Grid 5 **54.3 M4**	Grid 6 **53.8 M4**
Grid 7 **47.4 M4**	Grid 8 **54.1 M4**	Grid 9 **53.5 M4**

0 dB = 54.3V/m

Date/Time: 3/10/2010 8:56:22 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_UMTS_band_V_high chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF ER3D Device

Communication System: WCDMA FDD V; Frequency: 846.6 MHz;Duty Cycle: 1:1

Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 73.3 V/m; Power Drift = 0.016 dB

Maximum value of Total (measured) = 59.8 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 58.1 V/m

Probe Modulation Factor = 0.970

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 73.3 V/m; Power Drift = 0.016 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **48.7 M4**	Grid 2 **56.1 M4**	Grid 3 **55.7 M4**
Grid 4 **50.3 M4**	Grid 5 **58.1 M4**	Grid 6 **57.5 M4**
Grid 7 **50.3 M4**	Grid 8 **57.6 M4**	Grid 9 **56.9 M4**

0 dB = 58.1V/m

Date/Time: 3/10/2010 9:08:10 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_UMTS_band_V_high chan_Telecoil.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF ER3D Device

Communication System: WCDMA FDD V; Frequency: 846.6 MHz;Duty Cycle: 1:1

Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 73.7 V/m; Power Drift = -0.007 dB

Maximum value of Total (measured) = 60.0 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 58.3 V/m

Probe Modulation Factor = 0.970

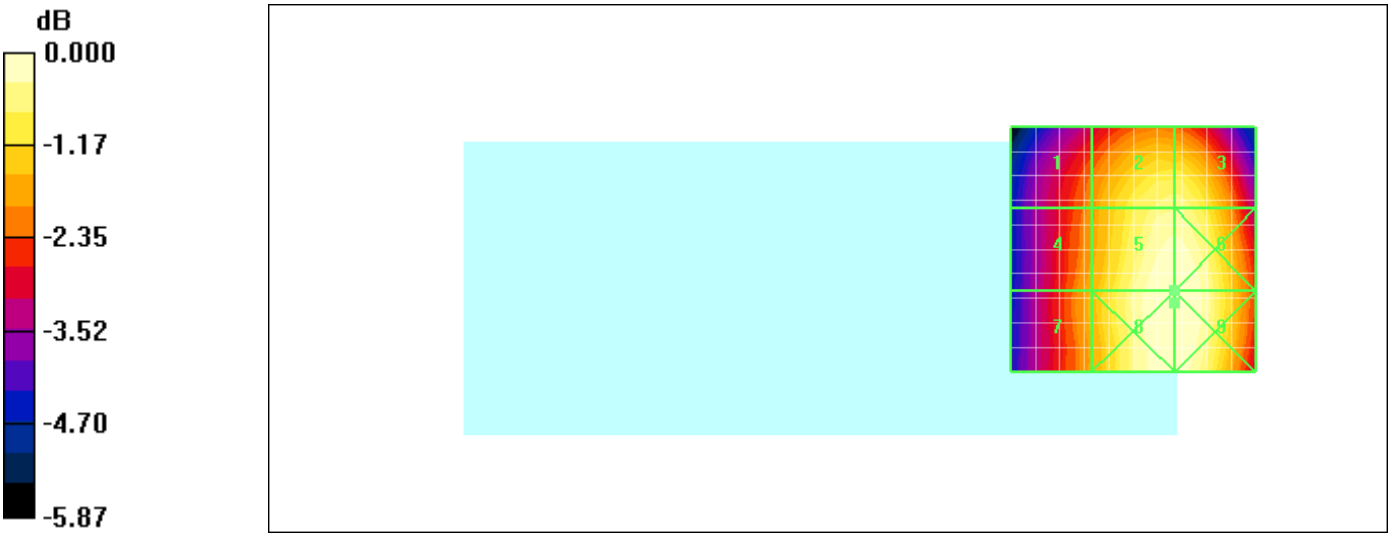
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 73.7 V/m; Power Drift = -0.007 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **46.1 M4**	Grid 2 **54.5 M4**	Grid 3 **54.5 M4**
Grid 4 **47.9 M4**	Grid 5 **58.3 M4**	Grid 6 **58.3 M4**
Grid 7 **48.2 M4**	Grid 8 **58.5 M4**	Grid 9 **58.5 M4**



0 dB = 58.5V/m

Date/Time: 3/10/2010 9:08:10 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_UMTS_band_V_high chan_Telecoil.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF ER3D Device

Communication System: WCDMA FDD V; Frequency: 846.6 MHz;Duty Cycle: 1:1

Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 73.7 V/m; Power Drift = -0.007 dB

Maximum value of Total (measured) = 60.0 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 58.3 V/m

Probe Modulation Factor = 0.970

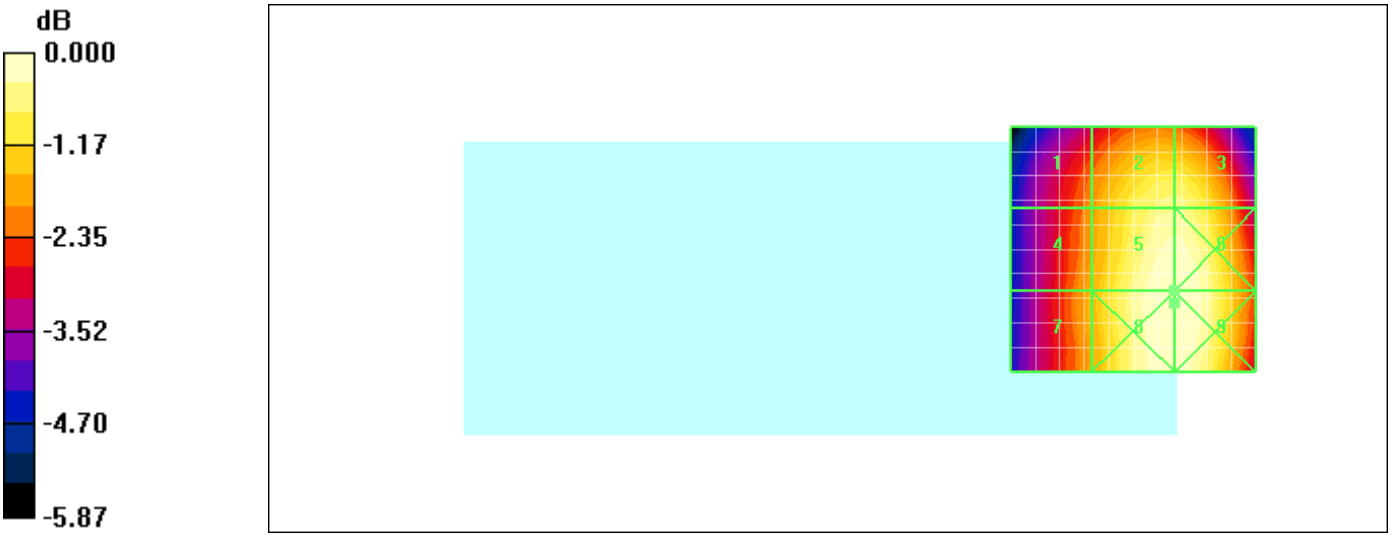
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 73.7 V/m; Power Drift = -0.007 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **46.1 M4**	Grid 2 **54.5 M4**	Grid 3 **54.5 M4**
Grid 4 **47.9 M4**	Grid 5 **58.3 M4**	Grid 6 **58.3 M4**
Grid 7 **48.2 M4**	Grid 8 **58.5 M4**	Grid 9 **58.5 M4**



0 dB = 58.5V/m

Date/Time: 3/10/2010 6:01:42 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_GSM_1900_low chan.da4

DUT: BlackBerry Smartphone

Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1850.2 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 17.1 V/m; Power Drift = 0.036 dB

Maximum value of Total (measured) = 36.3 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 69.5 V/m

Probe Modulation Factor = 2.66

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 17.1 V/m; Power Drift = 0.036 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **59.8 M3**	Grid 2 **56.9 M3**	Grid 3 **49.2 M3**
Grid 4 **46.7 M4**	Grid 5 **69.0 M3**	Grid 6 **69.5 M3**
Grid 7 **74.2 M3**	Grid 8 **96.8 M2**	Grid 9 **96.1 M2**

0 dB = 96.8V/m

Date/Time: 3/10/2010 6:09:55 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_GSM_1900_mid chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1880 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 16.6 V/m; Power Drift = 0.062 dB

Maximum value of Total (measured) = 30.1 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 60.7 V/m

Probe Modulation Factor = 2.66

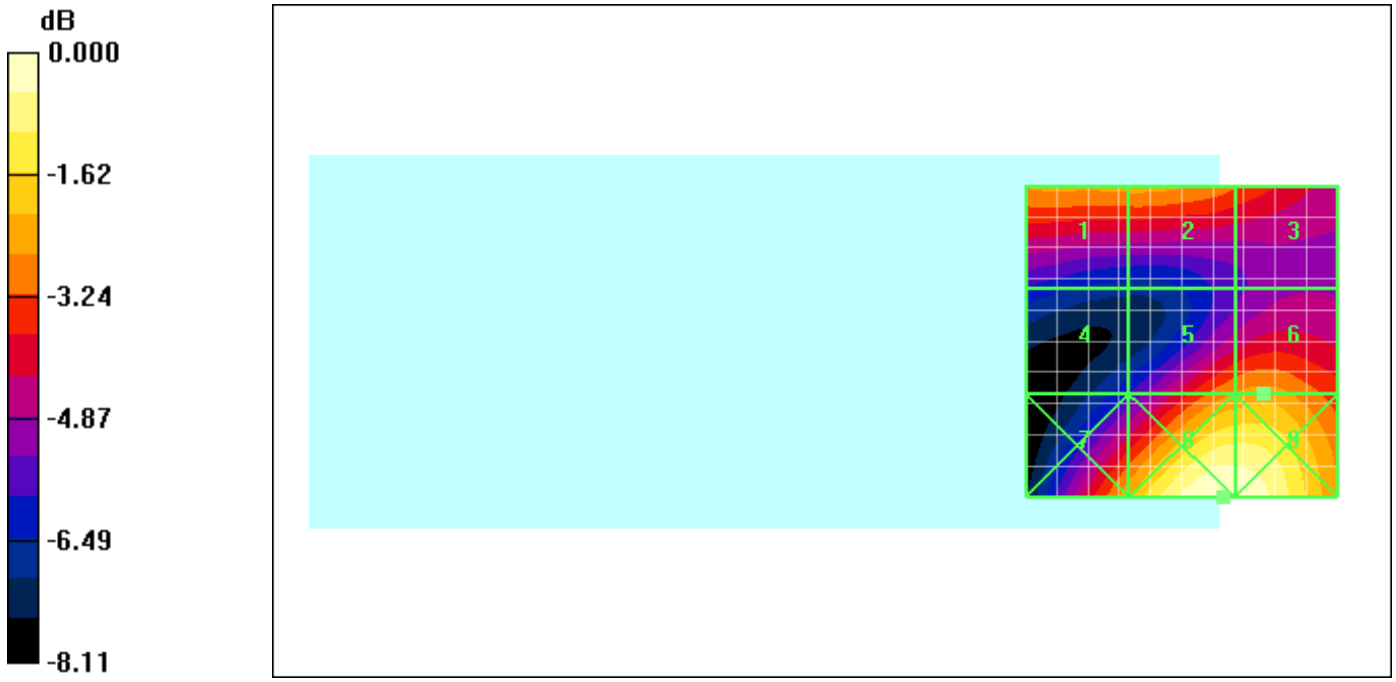
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 16.6 V/m; Power Drift = 0.062 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **60.5 M3**	Grid 2 **60.5 M3**	Grid 3 **55.9 M3**
Grid 4 **40.8 M4**	Grid 5 **59.2 M3**	Grid 6 **60.7 M3**
Grid 7 **62.0 M3**	Grid 8 **80.2 M3**	Grid 9 **79.8 M3**



0 dB = 80.2V/m

Date/Time: 3/10/2010 6:18:18 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_GSM_1900_high chan.da4

DUT: BlackBerry Smartphone

Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1909.8 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 14.3 V/m; Power Drift = -0.070 dB

Maximum value of Total (measured) = 27.3 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 56.2 V/m

Probe Modulation Factor = 2.66

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 14.3 V/m; Power Drift = -0.070 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **54.0 M3**	Grid 2 **56.2 M3**	Grid 3 **55.7 M3**
Grid 4 **39.5 M4**	Grid 5 **52.2 M3**	Grid 6 **53.6 M3**
Grid 7 **54.4 M3**	Grid 8 **73.1 M3**	Grid 9 **72.8 M3**

0 dB = 73.1V/m

Date/Time: 3/10/2010 6:28:07 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_GSM_1900_low chan_Telecoil.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF ER3D Device

Communication System: GSM 1900; Frequency: 1850.2 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 17.2 V/m; Power Drift = -0.057 dB

Maximum value of Total (measured) = 31.6 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 70.5 V/m

Probe Modulation Factor = 2.66

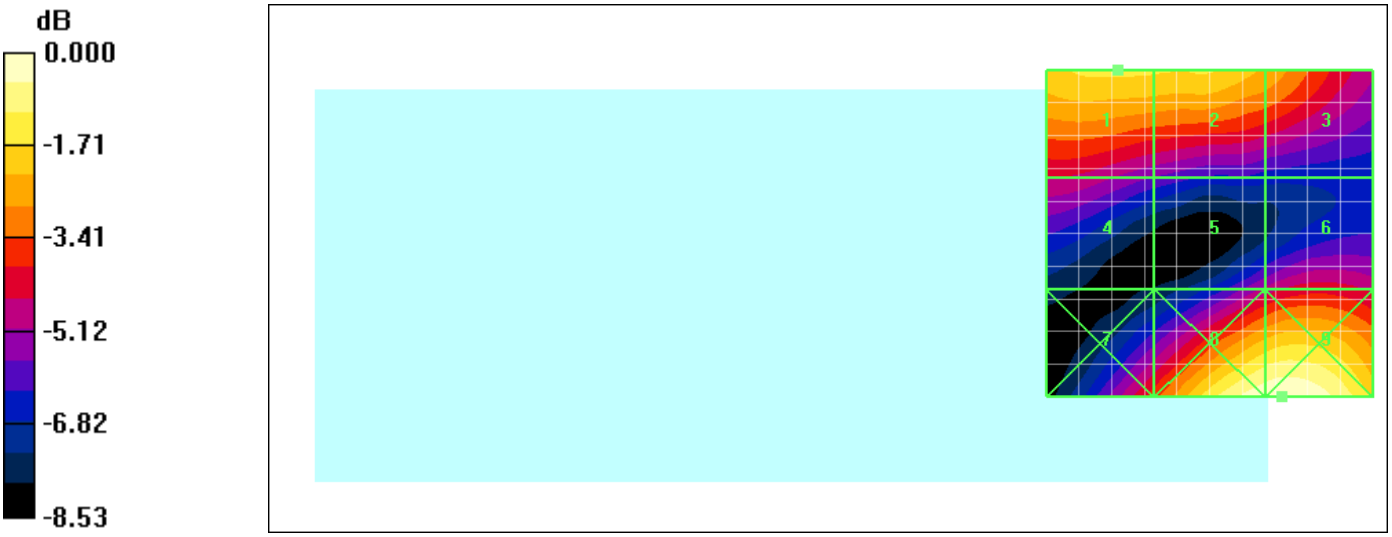
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 17.2 V/m; Power Drift = -0.057 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **70.5 M3**	Grid 2 **70.0 M3**	Grid 3 **64.1 M3**
Grid 4 **50.0 M3**	Grid 5 **47.8 M3**	Grid 6 **52.2 M3**
Grid 7 **55.9 M3**	Grid 8 **83.3 M3**	Grid 9 **84.3 M2**



0 dB = 84.3V/m

Date/Time: 3/10/2010 7:15:48 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_UMTS_band_II_low chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF ER3D Device

Communication System: WCDMA FDD II; Frequency: 1852.4 MHz;Duty Cycle: 1:1

Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 21.5 V/m; Power Drift = -0.062 dB

Maximum value of Total (measured) = 46.9 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 30.5 V/m

Probe Modulation Factor = 0.910

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 21.5 V/m; Power Drift = -0.062 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **27.8 M4**	Grid 2 **27.1 M4**	Grid 3 **24.5 M4**
Grid 4 **19.7 M4**	Grid 5 **30.2 M4**	Grid 6 **30.5 M4**
Grid 7 **33.5 M4**	Grid 8 **42.7 M4**	Grid 9 **42.3 M4**

0 dB = 42.7V/m

Date/Time: 3/10/2010 7:23:13 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_UMTS_band_II_mid chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF ER3D Device

Communication System: WCDMA FDD II; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 21.6 V/m; Power Drift = -0.029 dB

Maximum value of Total (measured) = 41.1 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 28.0 V/m

Probe Modulation Factor = 0.910

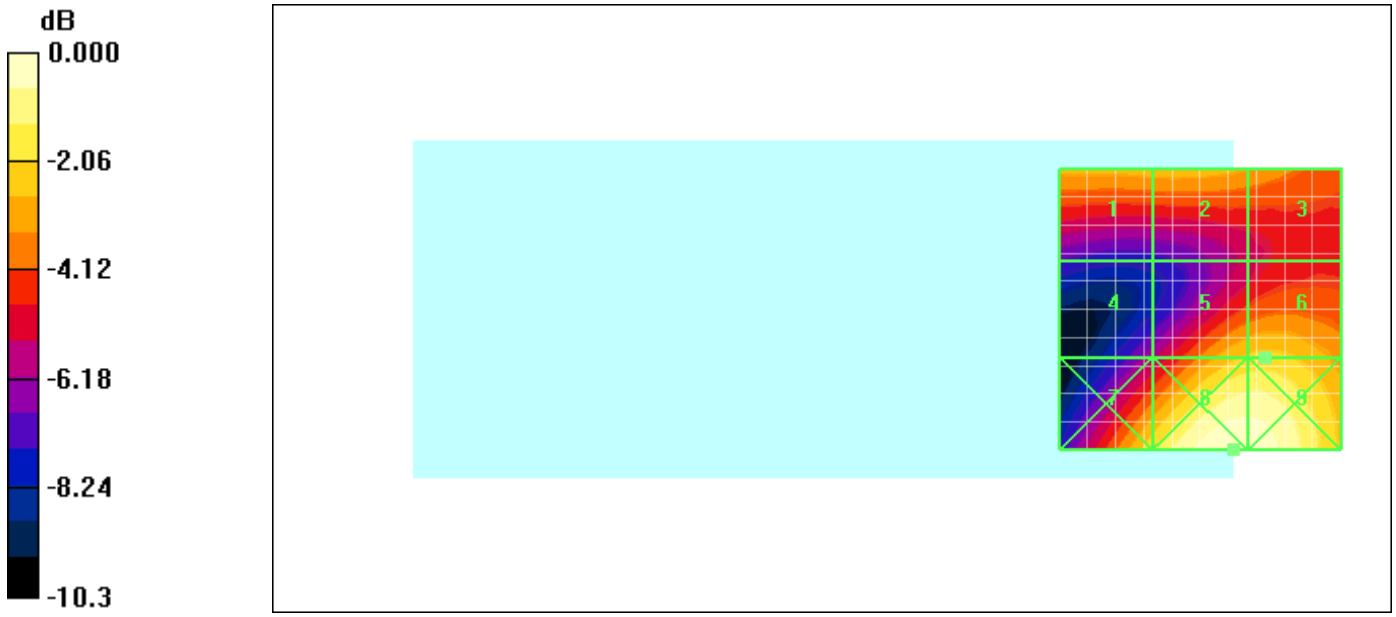
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 21.6 V/m; Power Drift = -0.029 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **26.3 M4**	Grid 2 **26.4 M4**	Grid 3 **25.2 M4**
Grid 4 **18.0 M4**	Grid 5 **27.6 M4**	Grid 6 **28.0 M4**
Grid 7 **29.0 M4**	Grid 8 **37.5 M4**	Grid 9 **37.2 M4**



0 dB = 37.5V/m

Date/Time: 3/10/2010 7:32:09 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_UMTS_band_II_high chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF ER3D Device

Communication System: WCDMA FDD II; Frequency: 1907.6 MHz;Duty Cycle: 1:1

Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 19.2 V/m; Power Drift = 0.001 dB

Maximum value of Total (measured) = 38.3 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 26.2 V/m

Probe Modulation Factor = 0.910

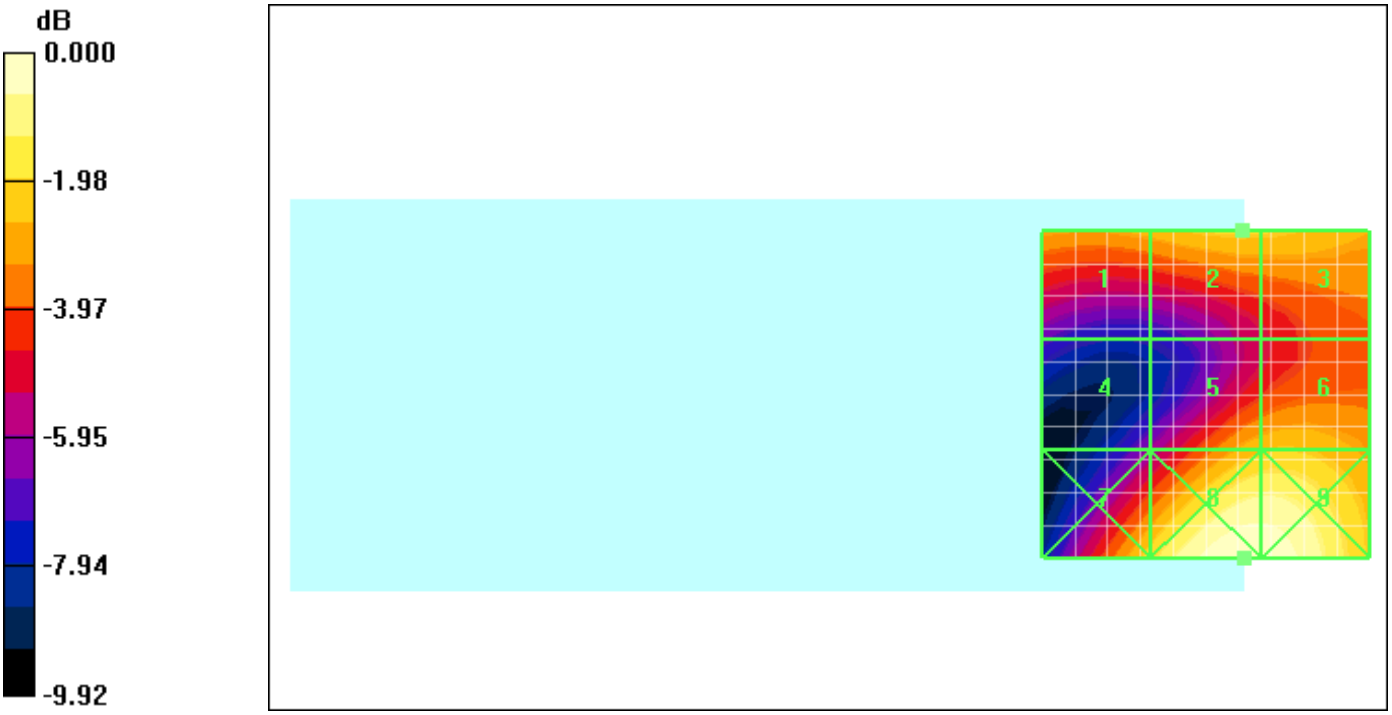
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 19.2 V/m; Power Drift = 0.001 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **24.6 M4**	Grid 2 **26.2 M4**	Grid 3 **26.1 M4**
Grid 4 **16.6 M4**	Grid 5 **25.3 M4**	Grid 6 **25.8 M4**
Grid 7 **27.0 M4**	Grid 8 **35.0 M4**	Grid 9 **34.7 M4**



0 dB = 35.0V/m

Date/Time: 3/10/2010 7:41:32 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_E_UMTS_band_II_low chan_Telecoil.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF ER3D Device

Communication System: WCDMA FDD II; Frequency: 1852.4 MHz;Duty Cycle: 1:1

Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/8/2010
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 21.4 V/m; Power Drift = -0.045 dB

Maximum value of Total (measured) = 41.2 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 33.1 V/m

Probe Modulation Factor = 0.910

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 21.4 V/m; Power Drift = -0.045 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 **33.1 M4**	Grid 2 **32.8 M4**	Grid 3 **29.9 M4**
Grid 4 **22.3 M4**	Grid 5 **21.8 M4**	Grid 6 **24.1 M4**
Grid 7 **24.2 M4**	Grid 8 **37.1 M4**	Grid 9 **37.6 M4**

0 dB = 37.6V/m

Date/Time: 3/10/2010 9:33:36 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_GSM_850_low_chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 824.2 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.052 A/m; Power Drift = 0.041 dB

Maximum value of Total (measured) = 0.102 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.206 A/m

Probe Modulation Factor = 2.79

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.052 A/m; Power Drift = 0.041 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.284 M4**	Grid 2 **0.206 M4**	Grid 3 **0.128 M4**
Grid 4 **0.254 M4**	Grid 5 **0.184 M4**	Grid 6 **0.113 M4**
Grid 7 **0.266 M4**	Grid 8 **0.189 M4**	Grid 9 **0.111 M4**

0 dB = 0.284A/m

Date/Time: 3/10/2010 9:45:06 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_GSM_850_mid_chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 836.8 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.052 A/m; Power Drift = -0.004 dB

Maximum value of Total (measured) = 0.107 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.217 A/m

Probe Modulation Factor = 2.79

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.052 A/m; Power Drift = -0.004 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.298 M4**	Grid 2 **0.217 M4**	Grid 3 **0.140 M4**
Grid 4 **0.262 M4**	Grid 5 **0.191 M4**	Grid 6 **0.118 M4**
Grid 7 **0.279 M4**	Grid 8 **0.195 M4**	**Grid 9** **0.107 M4**

0 dB = 0.298A/m

Date/Time: 3/10/2010 9:57:08 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_GSM_850_high_chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 848.8 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.059 A/m; Power Drift = 0.153 dB

Maximum value of Total (measured) = 0.111 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.228 A/m

Probe Modulation Factor = 2.79

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.059 A/m; Power Drift = 0.153 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.296 M4**	Grid 2 **0.218 M4**	Grid 3 **0.138 M4**
Grid 4 **0.279 M4**	Grid 5 **0.208 M4**	Grid 6 **0.133 M4**
Grid 7 **0.310 M4**	Grid 8 **0.228 M4**	Grid 9 **0.144 M4**

0 dB = 0.310A/m

Date/Time: 3/10/2010 10:06:08 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_GSM_850_high_chan_Telecoil.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: GSM 850; Frequency: 848.8 MHz;Duty Cycle: 1:8.3

Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.061 A/m; Power Drift = 0.038 dB

Maximum value of Total (measured) = 0.111 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.235 A/m

Probe Modulation Factor = 2.79

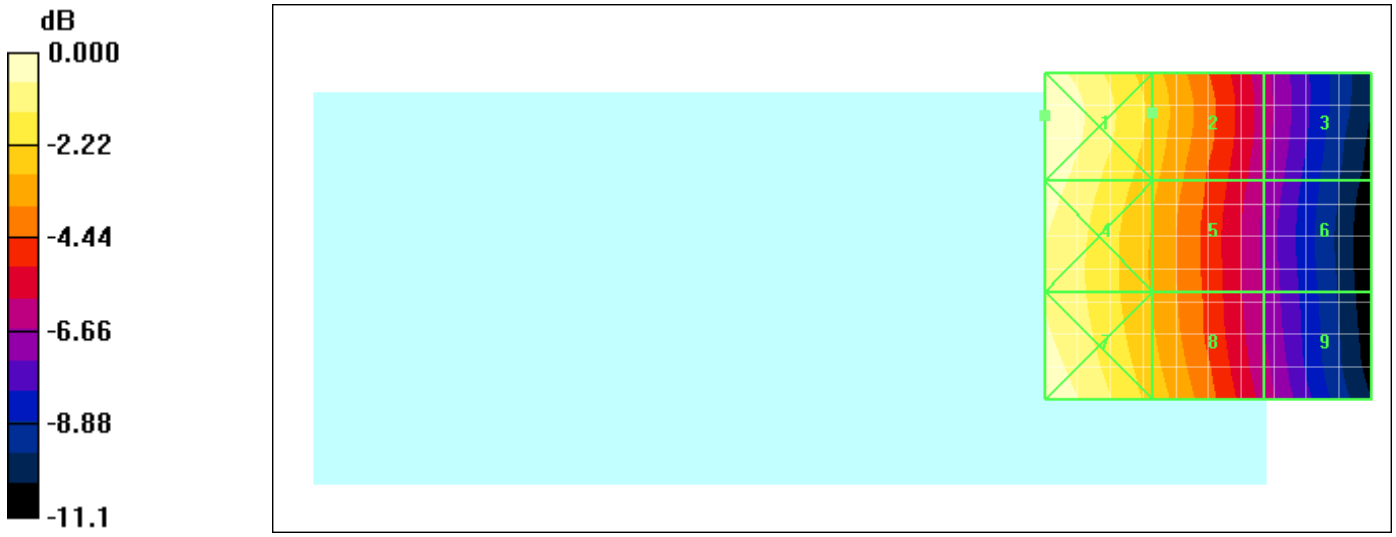
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.061 A/m; Power Drift = 0.038 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.310 M4**	Grid 2 **0.235 M4**	Grid 3 **0.151 M4**
Grid 4 **0.297 M4**	Grid 5 **0.225 M4**	Grid 6 **0.145 M4**
Grid 7 **0.305 M4**	Grid 8 **0.233 M4**	Grid 9 **0.153 M4**



0 dB = 0.310A/m

Date/Time: 3/10/2010 10:58:19 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_UMTS_band_V_low chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: WCDMA FDD V; Frequency: 826.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.044 A/m; Power Drift = -0.023 dB

Maximum value of Total (measured) = 0.088 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.064 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.044 A/m; Power Drift = -0.023 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.088 M4**	Grid 2 **0.064 M4**	Grid 3 **0.040 M4**
Grid 4 **0.078 M4**	Grid 5 **0.057 M4**	Grid 6 **0.034 M4**
Grid 7 **0.086 M4**	Grid 8 **0.061 M4**	Grid 9 **0.035 M4**

0 dB = 0.088A/m

Date/Time: 3/10/2010 11:05:05 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_UMTS_band_V_mid chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: WCDMA FDD V; Frequency: 836.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.045 A/m; Power Drift = 0.165 dB

Maximum value of Total (measured) = 0.092 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.067 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.045 A/m; Power Drift = 0.165 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.092 M4**	Grid 2 **0.067 M4**	Grid 3 **0.044 M4**
Grid 4 **0.080 M4**	Grid 5 **0.058 M4**	Grid 6 **0.037 M4**
Grid 7 **0.086 M4**	Grid 8 **0.061 M4**	Grid 9 **0.034 M4**

0 dB = 0.092A/m

Date/Time: 3/10/2010 11:12:08 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_UMTS_band_V_high chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: WCDMA FDD V; Frequency: 846.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.056 A/m; Power Drift = 0.062 dB

Maximum value of Total (measured) = 0.104 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.077 A/m

Probe Modulation Factor = 1.00

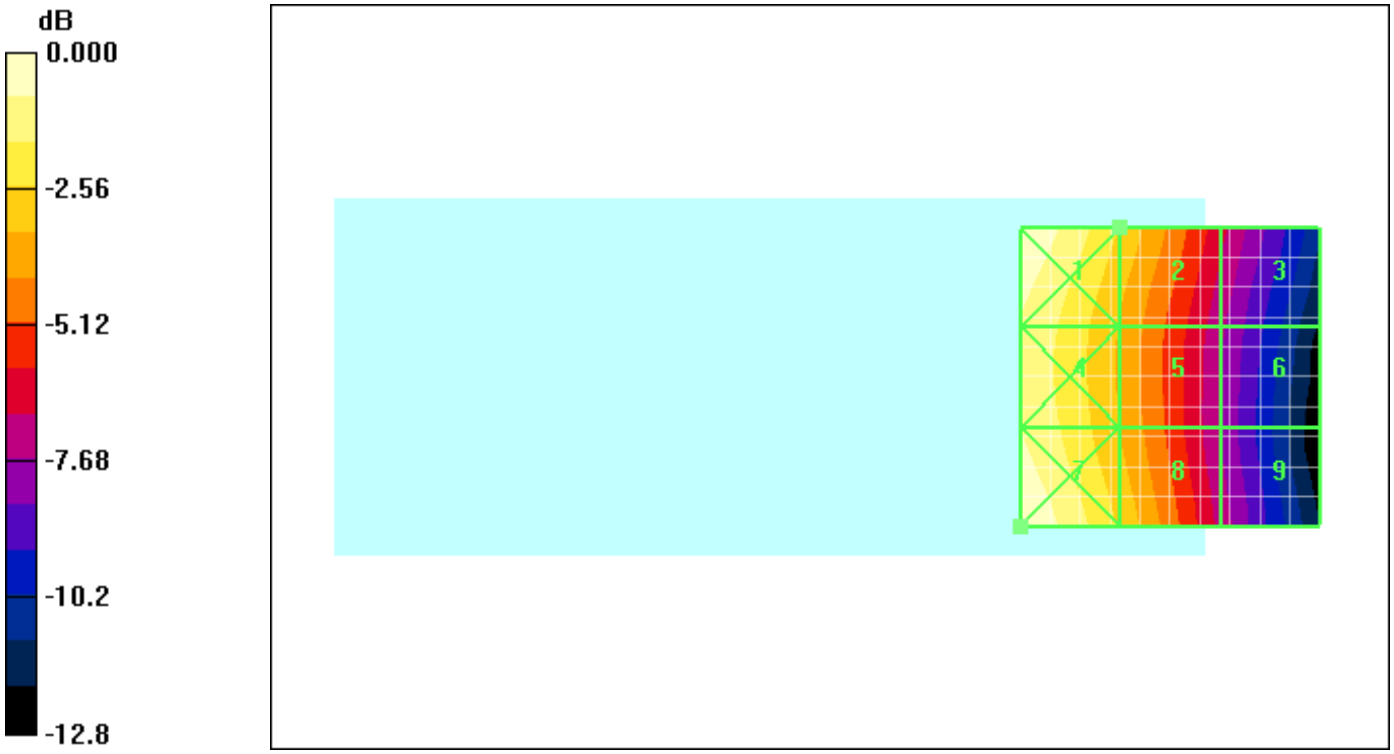
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.056 A/m; Power Drift = 0.062 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.104 M4**	Grid 2 **0.077 M4**	Grid 3 **0.049 M4**
Grid 4 **0.094 M4**	Grid 5 **0.070 M4**	Grid 6 **0.044 M4**
Grid 7 **0.104 M4**	Grid 8 **0.077 M4**	Grid 9 **0.046 M4**



0 dB = 0.104A/m

Date/Time: 3/10/2010 11:18:01 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_UMTS_band_V_high chan_Telecoil.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: WCDMA FDD V; Frequency: 846.6 MHz;Duty Cycle: 1:1

Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.056 A/m; Power Drift = -0.015 dB

Maximum value of Total (measured) = 0.108 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.083 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.056 A/m; Power Drift = -0.015 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.108 M4**	Grid 2 **0.083 M4**	Grid 3 **0.054 M4**
Grid 4 **0.101 M4**	Grid 5 **0.077 M4**	Grid 6 **0.050 M4**
Grid 7 **0.103 M4**	Grid 8 **0.078 M4**	Grid 9 **0.049 M4**

0 dB = 0.108A/m

Date/Time: 3/10/2010 10:14:42 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_GSM_1900_low_chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1850.2 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.078 A/m; Power Drift = -0.151 dB

Maximum value of Total (measured) = 0.080 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.192 A/m

Probe Modulation Factor = 2.42

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.078 A/m; Power Drift = -0.151 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.142 M3**	Grid 2 **0.192 M3**	Grid 3 **0.194 M3**
Grid 4 **0.140 M4**	Grid 5 **0.192 M3**	Grid 6 **0.194 M3**
Grid 7 **0.191 M3**	Grid 8 **0.164 M3**	Grid 9 **0.166 M3**

0 dB = 0.194A/m

Date/Time: 3/10/2010 10:21:20 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_GSM_1900_mid_chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1880 MHz;Duty Cycle: 1:8.3

Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.074 A/m; Power Drift = -0.097 dB

Maximum value of Total (measured) = 0.074 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.180 A/m

Probe Modulation Factor = 2.42

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.074 A/m; Power Drift = -0.097 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.160 M3**	Grid 2 **0.180 M3**	Grid 3 **0.180 M3**
Grid 4 **0.143 M3**	Grid 5 **0.179 M3**	Grid 6 **0.180 M3**
Grid 7 **0.157 M3**	Grid 8 **0.154 M3**	Grid 9 **0.154 M3**

0 dB = 0.180A/m

Date/Time: 3/10/2010 10:28:06 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_GSM_1900_high_chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1909.8 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.069 A/m; Power Drift = -0.072 dB

Maximum value of Total (measured) = 0.069 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.165 A/m

Probe Modulation Factor = 2.42

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.069 A/m; Power Drift = -0.072 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.156 M3**	Grid 2 **0.165 M3**	Grid 3 **0.167 M3**
Grid 4 **0.130 M4**	Grid 5 **0.165 M3**	Grid 6 **0.167 M3**
Grid 7 **0.155 M3**	Grid 8 **0.148 M3**	Grid 9 **0.149 M3**

0 dB = 0.167A/m

Date/Time: 3/10/2010 10:37:03 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_GSM_1900_low_chan_Telecoil.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: GSM 1900; Frequency: 1850.2 MHz;Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.078 A/m; Power Drift = 0.062 dB

Maximum value of Total (measured) = 0.082 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.189 A/m

Probe Modulation Factor = 2.42

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.078 A/m; Power Drift = 0.062 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.147 M3**	Grid 2 **0.186 M3**	Grid 3 **0.194 M3**
Grid 4 **0.133 M4**	Grid 5 **0.189 M3**	Grid 6 **0.198 M3**
Grid 7 **0.156 M3**	Grid 8 **0.182 M3**	Grid 9 **0.188 M3**

0 dB = 0.198A/m

Date/Time: 3/10/2010 11:24:29 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_UMTS_band_II_low chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: WCDMA FDD II; Frequency: 1852.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.102 A/m; Power Drift = -0.084 dB

Maximum value of Total (measured) = 0.102 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.099 A/m

Probe Modulation Factor = 0.970

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.102 A/m; Power Drift = -0.084 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.081 M4**	Grid 2 **0.099 M4**	Grid 3 **0.099 M4**
Grid 4 **0.077 M4**	Grid 5 **0.099 M4**	Grid 6 **0.099 M4**
Grid 7 **0.092 M4**	Grid 8 **0.086 M4**	Grid 9 **0.086 M4**

0 dB = 0.099A/m

Date/Time: 3/10/2010 11:30:41 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_UMTS_band_II_mid chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: WCDMA FDD II; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.094 A/m; Power Drift = 0.075 dB

Maximum value of Total (measured) = 0.096 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.093 A/m

Probe Modulation Factor = 0.970

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.094 A/m; Power Drift = 0.075 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.082 M4**	Grid 2 **0.093 M4**	Grid 3 **0.093 M4**
Grid 4 **0.074 M4**	Grid 5 **0.093 M4**	Grid 6 **0.093 M4**
Grid 7 **0.083 M4**	Grid 8 **0.080 M4**	Grid 9 **0.080 M4**

0 dB = 0.093A/m

Date/Time: 3/10/2010 11:37:57 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_UMTS_band_II_high chan.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: WCDMA FDD II; Frequency: 1907.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.091 A/m; Power Drift = -0.159 dB

Maximum value of Total (measured) = 0.091 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.088 A/m

Probe Modulation Factor = 0.970

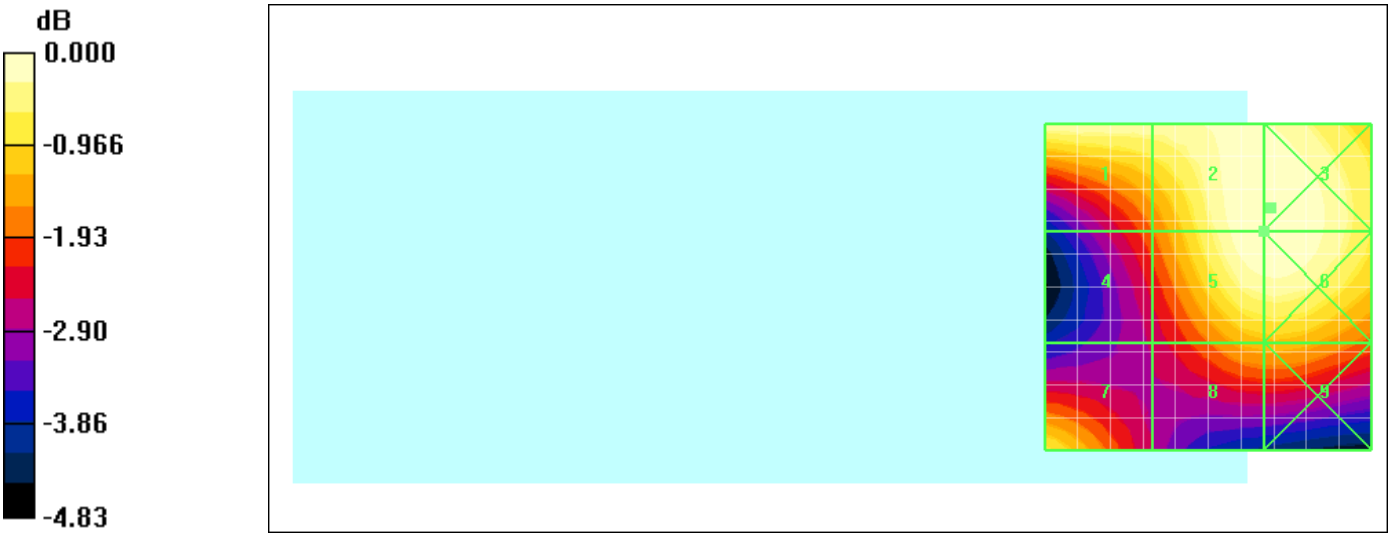
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.091 A/m; Power Drift = -0.159 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.085 M4**	Grid 2 **0.088 M4**	Grid 3 **0.088 M4**
Grid 4 **0.071 M4**	Grid 5 **0.088 M4**	Grid 6 **0.088 M4**
Grid 7 **0.080 M4**	Grid 8 **0.075 M4**	Grid 9 **0.075 M4**



0 dB = 0.088A/m

Date/Time: 3/10/2010 11:45:55 PM

Test Laboratory: RIM TESTING SERVICES

File Name: HAC_H_UMTS_band_II_low chan_Telecoil.da4

DUT: BlackBerry Smartphone;

Program Name: HAC RF H3DV6 Device

Communication System: WCDMA FDD II; Frequency: 1852.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3

Phantom section: RF Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/13/2009
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn473; Calibrated: 1/4/2010
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid: dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.102 A/m; Power Drift = -0.116 dB

Maximum value of Total (measured) = 0.103 A/m

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.097 A/m

Probe Modulation Factor = 0.970

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.102 A/m; Power Drift = -0.116 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 **0.088 M4**	Grid 2 **0.096 M4**	Grid 3 **0.099 M4**
Grid 4 **0.074 M4**	Grid 5 **0.097 M4**	Grid 6 **0.100 M4**
Grid 7 **0.077 M4**	Grid 8 **0.093 M4**	Grid 9 **0.095 M4**

0 dB = 0.100A/m